

SMIC 40nm Low Leakage HS LVT  
Logic Process  
Standard Cell Library Databook  
V0.2



## **DISCLAIMER**

SMIC hereby provides the quality information to you but makes no claims, promises or guarantees about the accuracy, completeness, or adequacy of the information herein. The information contained herein is provided on an “AS IS” basis without any warranty, and SMIC assumes no obligation to provide support of any kind or otherwise maintain the information. SMIC disclaims any representation that the information does not infringe any intellectual property rights or proprietary rights of any third Parties. SMIC makes no other warranty, whether express, implied or statutory as to any matter whatsoever, including but not limited to the accuracy or sufficiency of any information or the merchantability and fitness for a particular purpose. Neither SMIC nor any of its representatives shall be liable for any cause of action incurred to connect to this service.

## **STATEMENT OF USE AND CONFIDENTIALITY**

The following/attached material contains confidential and proprietary information of SMIC. This material is based upon information, which SMIC considers reliable, but SMIC neither represents nor warrants that such information is accurate or complete, and it must not be relied upon as such. This information was prepared for informational purposes and is for the use by SMIC’s customer only. SMIC reserves the right to make changes in the information at any time without notice. No part of this information may be reproduced, transmitted, transcribed, stored in a retrieval system, or translated into any human or computer language, in any form or by any means, electronic, mechanical, magnetic, optical, chemical, manual, or otherwise, without the prior written consent of SMIC. Any unauthorized use or disclosure of this material is strictly prohibited and may be unlawful. By accepting this material, the receiving party shall be deemed to have acknowledged, accepted, and agreed to be bound by the foregoing limitations and restrictions. Thank you.

**Note:** SMIC is not in the position to guarantee the silicon verified IP will work in any design environment or certain production yield ratio. In addition, we are not responsible for commitments made to customers by IP providers.

Semiconductor Manufacturing International Corporation  
No. 18 Zhangjiang Road  
Pudong New Area  
Shanghai, 201203  
People’s Republic of China

# Revision History

This document contains the release history for SMIC 40nm low leakage HS RVT Process Standard Cell Library Databook.

IP Code	Release Version	Date of Release	Update Description
SCC40NLL_HS_LVT	0.0	Oct, 2010	Initial Release
SCC40NLL_HS_LVT	0.1	May, 2011	Update Release: New spice model
SCC40NLL_HS_LVT	0.2	Oct, 2012	Update Release: 1, Enrich cell functions 2, Improve cell performance 3, Optimize cell physical layout 4, New spice model (1.41r)

# Table of Contents

REVISION HISTORY .....	3
TABLE OF CONTENTS .....	4
INTRODUCTION .....	7
ORGANIZATION OF THE DATABOOK .....	7
GLOBAL PARAMETERS .....	7
PHYSICAL CELL SPECIFICATIONS .....	7
TIMING CONSTRAINS .....	8
NAMING CONVENTIONS .....	11
SPECIAL CELLS .....	13
STANDARD CELL DATASHEET .....	15
LVT_AD1HS .....	15
LVT_ADH1HS .....	17
LVT_AND2HS .....	19
LVT_AND3HS .....	21
LVT_AND4HS .....	23
LVT_AOI21HS .....	25
LVT_AOI211HS .....	27
LVT_AOI22HS .....	29
LVT_AOI221HS .....	31
LVT_AOI222HS .....	33
LVT_AOI31HS .....	35
LVT_AOI32HS .....	37
LVT_AOI33HS .....	39
LVT_BUFHS .....	41
LVT_CLKAND2HS .....	43
LVT_CLKBUFHS .....	45
LVT_CLKNHS .....	47
LVT_CKMUX2HS .....	49
LVT_CLKNAND2HS .....	51
LVT_CLKXOR2HS .....	53
LVT_CLKLANQHS .....	55
LVT_DELHS .....	58
LVT_DHS .....	59
LVT_DQHS .....	61
LVT_DXHS .....	63
LVT_DRNHS .....	65
LVT_DRNQHS .....	67
LVT_DRSNHS .....	69
LVT_DSNHS .....	71
LVT_I2NAND4HS .....	73

LVT_I2NOR4HS .....	75
LVT_IAO21HS .....	77
LVT_IAO22HS .....	79
LVT_INAND2HS.....	81
LVT_INAND3HS.....	83
LVT_INAND4HS.....	85
LVT_INOR2HS.....	87
LVT_INOR3HS.....	89
LVT_INOR4HS.....	91
LVT_INHS .....	93
LVT_IOA21HS .....	95
LVT_IOA22HS .....	97
LVT_LALHS.....	99
LVT_LALRNHS .....	101
LVT_LALRSNHS.....	103
LVT_LALSNHS.....	105
LVT_MAOI22HS.....	107
LVT_MAOI222HS .....	109
LVT_MOAI22HS.....	111
LVT_MUX2HS .....	113
LVT_MUX2NHS .....	115
LVT_MUX3HS .....	117
LVT_MUX3NHS .....	119
LVT_MUX4HS .....	121
LVT_MUX4NHS .....	123
LVT_NAND2HS.....	125
LVT_NAND3HS.....	127
LVT_NAND4HS.....	129
LVT_NOR2HS .....	131
LVT_NOR3HS.....	133
LVT_NOR4HS .....	135
LVT_OAI21HS .....	137
LVT_OAI211HS.....	139
LVT_OAI22HS .....	141
LVT_OAI221HS .....	143
LVT_OAI222HS .....	145
LVT_OAI31HS .....	147
LVT_OAI32HS .....	149
LVT_OAI33HS .....	151
LVT_OR2HS.....	153
LVT_OR3HS.....	155
LVT_OR4HS.....	157
LVT_SDHS .....	159
LVT_SDQHS.....	161
LVT_SDXHS.....	163
LVT_SDRNHS.....	166
LVT_SDRNQHS .....	168
LVT_SDRSNHS.....	170

LVT_SDSNHS .....	173
LVT_TBUFHS .....	175
LVT_XNOR2HS .....	177
LVT_XNOR3HS .....	179
LVT_XNOR4HS .....	181
LVT_XOR2HS .....	183
LVT_XOR3HS .....	185
LVT_XOR4HS .....	187

# Introduction

SMIC's standard cell library is custom-designed and tested to provide the optimum combination of high-performance and high-density cells. Cell optimization is derived from extensive internal and external custom designs and place-and-route analysis; whereas, library optimization is characterized by thorough simulation of library functions and of various drive strengths using leading simulation and place-and-route tools to produce superior GDSII results.

## Organization of the databook

The introduction is organized into several sections:

1. Global Parameters provides library overview and some general specifications.
2. Timing Constraint describes what type of timing specification is measured from each cell.
3. Naming Conventions provides standard cells' name conventions.
4. Special Cells defines the various types of special cells in the library.
5. Standard Cell Library Interpretation explains the components in each of the datasheets.

## Global Parameters

This section defines the general specifications for the SMIC 40nm Low Leakage HS LVT Process Standard Cell Library. It includes physical cell specifications, electrical specifications, propagation delay specifications, timing specifications, and power calculation.

## Physical Cell Specifications

Table 1. shows the physical design cell specification for this standard cell library.

**Table 1. Physical Cell Specification**

Drawn Gate Length (um)	0.04
Number of Layers of Metal	6,7,8,9 or 10
Layout Grid (um)	0.005
Vertical Pin Grid (um)	0.14n+0.07
Horizontal Pin Grid (um)	0.14n+0.07
Cell power and Ground Rail Width (um)	0.14
Cell Height (um)	1.26
N-well and substrate distance	10.0

Where n is positive integer value. All pins are located with a 0.07um offset to vertical and horizontal pin grids, making place-and-route tools much more efficient.

### Note

The library supports designs with six, seven, eight, nine, or ten layers of metal. For different layers of top-level metal, it is possible that a change in the design rules description within the technology file is required, because the top metal has greater minimum width, minimum spacing, and minimum area requirements. Please refer to "40nm Logic Salicide 0.9/1.1/1.2/1.8/2.5V Low Leakage and Generic Design Rule" for more information. It is crucial to define these rules correctly within the technology file for the place-and-route tool to function properly.

Table 2. lists the electrical specifications for this standard cell library.

**Table 2. Electrical Specifications**

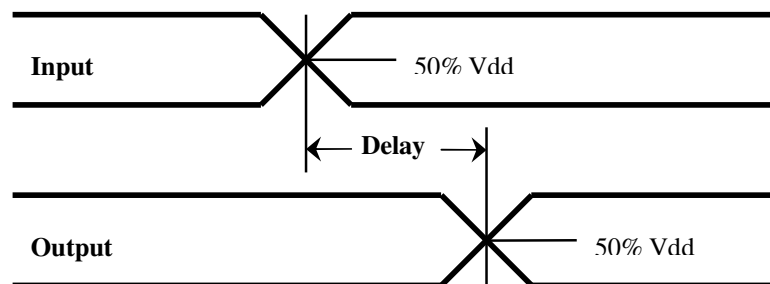
<b>Corners</b>	<b>Best Low Temp</b>	<b>Best High Temp</b>	<b>Best: Zero Temp</b>	<b>Typical</b>	<b>Typical High Temp</b>	<b>Worst Low Temp</b>	<b>Worst High Temp</b>
Supply Voltage ( V )	1.21	1.21	1.21	1.10	1.10	0.99	0.99
Junction Temperature ( °C )	-40	125	0	25	125	-40	125

## Timing Constrains

### Propagation Delay and Transition Time

Propagation delay is the sum of the intrinsic delay, the load delay, and the input-slew delay of a cell. Delays are defined as the time interval between the input stimulus and output crossing 50% of the Vdd value. The propagation delay is illustrated in Figure 1. below.

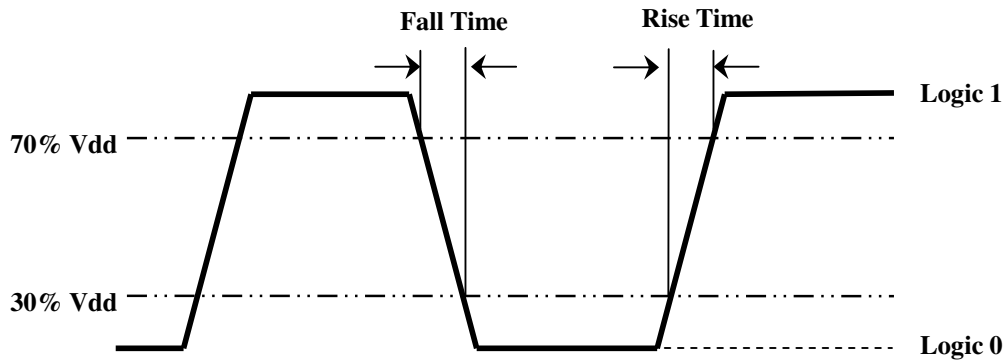
**Figure 1. Propagation Delay**



Transition time or slew rate is defined as the time interval between crossings of 30% to 70% of Vdd value on a signal. Transition time is shown in Figure 2. for both rising and falling signals.



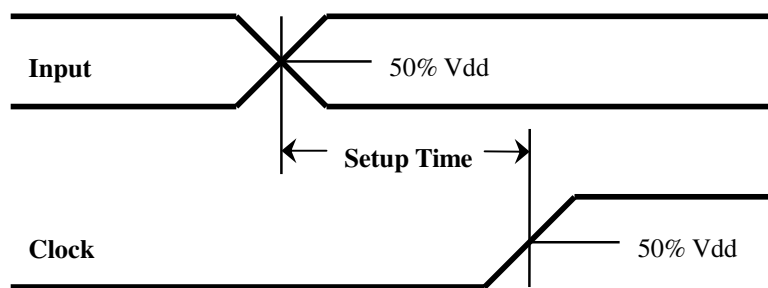
**Figure 2. Transition Time**



## Setup Time

Setup time for a sequential cell is the minimum period of time the data signal must remain stable before the active edge of the clock (or another specified signal) to ensure correct function at the output. Setup constraint values are measured as the interval between the data signal crossing 50% of V<sub>dd</sub> for rising or falling data and the clock signal crossing 50% of V<sub>dd</sub> for rising or falling clocks. For measurement of setup time, the data signal is kept stable indefinitely after the clock edge. Definition of setup time for a positive-edge triggered sequential cell is shown in Figure 3.

**Figure 3. Setup Time**

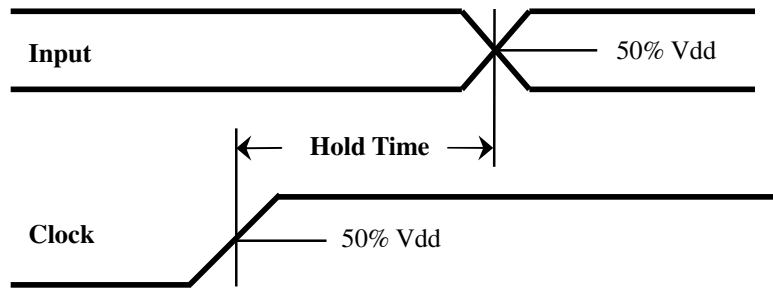


## Hold Time

Hold time for a sequential cell is the minimum period of time the data signal must remain stable after the active edge of the clock (or another specified signal) to ensure correct function at the output. Hold constraint values are measured as the interval between the data signal crossing 50% of V<sub>dd</sub> value and the clock signal crossing 50% of V<sub>dd</sub> for either rise or fall transitions on both signals. For measurement of hold time, the data signal is kept stable indefinitely before the clock

edge. Definition of fall time for a positive-edge triggered sequential cell is shown in Figure 4.

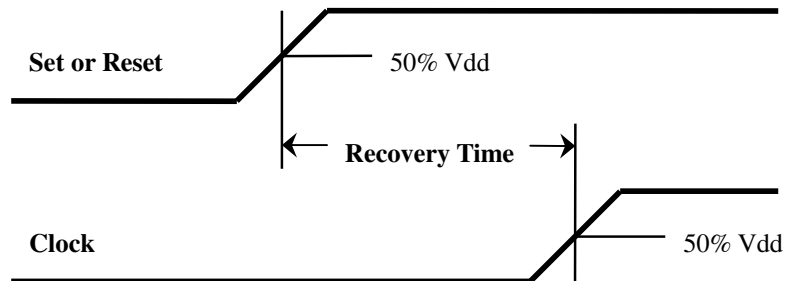
**Figure 4. Hold Time**



## Recovery Time

Recovery time for sequential cell is the minimum length of time that the active-low set or reset signal must remain high before the active edge of the clock to ensure correct cell function. Recovery constraint value is measured as the interval between the set or reset signal crossing 50% of Vdd and the clock signal crossing 50% of Vdd for rising or falling clocks. For measurement of recovery time, the set or reset signal is held stable indefinitely after the clock edge. Definition of recovery time is shown below in Figure 5.

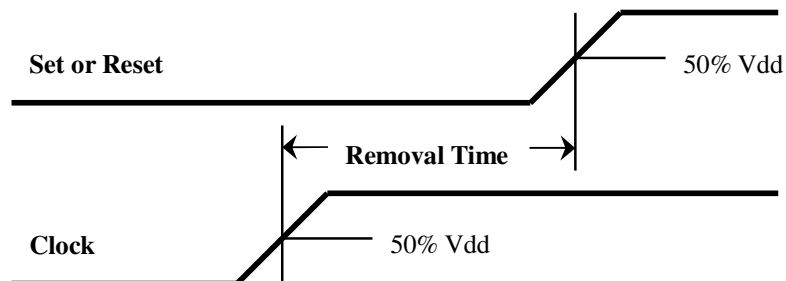
**Figure 5. Recovery Time**



## Removal Time

Removal time for sequential cell is the minimum length of time that the set or reset signals must remain low after the active edge of the clock to ensure correct cell function. Removal constraint value is measured as the interval between the set or reset signal crossing 50% of Vdd and the clock signal crossing 50% of Vdd for rising or falling clocks. For measurement of removal time, the set or reset signal is held stable indefinitely before the clock edge. Definition of removal time is shown in Figure 6.

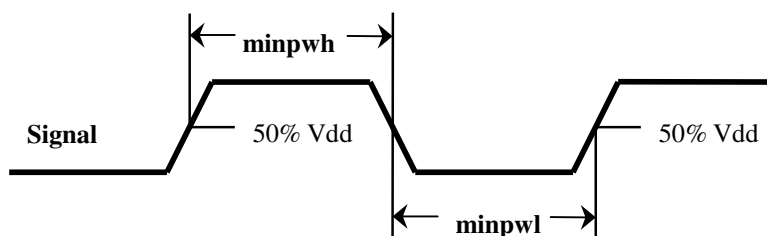
**Figure 6. Removal Time**



## Minimum Pulse Width

Minimum pulse width is the minimum period of time between the leading and trailing edges of a pulse waveform. Minimum pulse width high (minpwh) is measured as the interval between the rising edge of signal crossing 50% of Vdd and the falling edge of signal crossing 50% of Vdd. Minimum pulse width low (minpwl) is measured as the interval between the falling edge of signal crossing 50% of Vdd and the rising edge of signal crossing 50% of Vdd. Minimum pulse width is illustrated in Figure 7.

**Figure 7. Minimum Pulse Width**



## Naming Conventions

This section provides the naming convention for SMIC 40nm Low Leakage Process HS LVT Standard Cell Library. The syntax is: <Cell Type><Options> <library family> <Drive Selection>

### Example:

**AND2HSV1:** AND is Cell Type, 2 is the number of inputs, HS is High-Speed library and V1 is driving strength.

Cell Type	Description	Options
INV	Inverter cell	CKINV :Inverting Clock Inverter TINV: Tri-state inverter
BUF	Buffer cell	CLKBUF: Clock buffer TBUF: Tri-state buffer

AND	AND cell	2/3/4: The number of input pins
NAND	NAND cell	2/3/4: The number of input pins
I2NAND	NAND cell	3/4: with 2 Inverted Inputs
OR	OR cell	2/3/4: The number of input pins
NOR	NOR cell	2/3/4: The number of input pins
AO	AND-OR cell	21/211/221: The number of AND groups and additional inputs
OA	OR-AND cell	21/211/221: The number of OR groups and additional inputs
AOI	AND-OR-Inverter cell	21/211/221: The number of AND groups and additional inputs
OAI	OR-AND-Inverter cell	21/211/221: The number of OR groups and additional inputs
XOR	Exclusive OR cell	2/3:The number of input pins
XNOR	Exclusive NOR cell	2/3:The number of input pins
DEL	Delay cell	1/2/3/4: Delay class
AC	Full adder carry-generator	AC1CIN:with active low carry-in (CIN) AC1CON: with carry in (CI)
AD	Full adder cell	AD1CSCIN: with CO and CIN AD1CON: with CON and CI AD2 provides a carry-select adder function
ADH	Half adder cell	ADH1CIN with CO and CIN ADH1CON with CON and CI
MUX	Multiplexer cell	2/4:The number of input pins N: Inverted
D	Flip-Flop cell	SD: D flip-flop with scan ED: D flip-flop with enable SED: D flip-flop with scan enable DN: Negative edge clock trigger DQ: Output Q only DG: With synchronous (Reset/Set) S: Set R: Reset X: Mux Inputs
LA	Transparent Latch cell	L: Active low enable H: Active high enable CLKLA: Clock-gating latch R: Reset S: Set T: Tri-state transparent latch
HOLD	Weak bus holder	

**All cells' names must be in upper case. For flip-flop cells, the default is:**

Positive edge clock trigger  
Asynchronous Set or Reset  
With Q and QN

**For latch cells, the default is:**

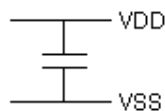
Active high enable  
Asynchronous Set or Reset

# Special Cells

This section discusses the special cell types within the SMIC Standard Cell Library.

## De-CAP Cells

The standard cell library includes 5 De-CAP cells: LVT\_FDCAPHS4, LVT\_FDCAPHS8, LVT\_FDCAPHS16, LVT\_FDCAPHS32 and LVT\_FDCAPHS64. De-CAP is composed of a PMOS and NMOS device to form decoupling capacitors between  $V_{DD}$  and  $V_{SS}$  rails so as to reduce the voltage bounce on the power rails. The De-CAP functional schematic is shown in Figure 8. below.



**Figure 8. De-CAP Functional Schematic**

## FILL Cells

The standard cell library includes 5 FILL cells, namely: LVT\_F\_FILLHS1, LVT\_F\_FILLHS2, LVT\_F\_FILLHS4, LVT\_F\_FILLHS8 and LVT\_F\_FILLHS16. The number denoted at the end of the cell names represents the width of the cell measured in number of tracks.

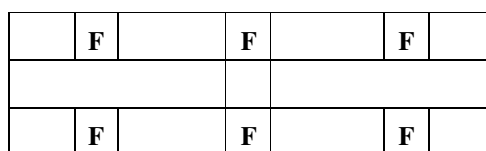
The FILL cells are used to connect power and ground rails across an area with no cells during place and route. It is used to ensure that gaps do not occur between well or implant layers which in some cases can cause DRC violations.

### PULL0/1 Cells

The LVT\_PULLHS0 and LVT\_PULLHS1 cells provide ESD protection of signal inputs from power and ground rails. These cells provide diffusion-driven inputs for signal pins. If these cells are not used and Via(s) are dropped on the power rails, DRC error or shorts may occur. Any input pin that will be preset to 0/1 need connect LVT\_PULLHS0 / LVT\_PULLHS1 cell rather than VSS/VDD.

## NWELL and Substrate Tie Cells

The standard cell library contains one NWELL/Substrate Tie Cell: LVT\_FILLTIEHS. This standard cell library does not have well or substrate ties inside the cells. It is required to tie NWell to VDD and substrate to VSS before place-and-route using the LVT\_FILLTIEHS cells. It is also required to place the Tie cells as frequent as the design requires. Figures 9 and 10 illustrate the two LVT\_FILLTIEHS cell orientations within the library.



**Figure 9. Normal placement of FILLTIE cells**

	<b>F</b>				<b>F</b>	
			<b>t</b>			
	<b>F</b>				<b>F</b>	

**Figure 10. Flipped placement of FILLTIE cells**

Figure 9 shows that normal placement of FILLTIEHS cells requires tie cells be placed every 20um. The accurate data please refer to "40nm Logic Salicide 0.9/1.0/1.1/1.2/1.8/2.5V Low leakage and generic ESD and Latch-up Guidelines". All rows except for the top and bottom two have their VDD and VSS shared between the adjacent rows, allowing for wider placement of LVT\_FILLTIEHS cells when the cells of alternating rows are placed with an offset, as illustrated above in Figure 10. An example of this would be that the design rule specifies LVT\_FILLTIEHS cells every 20um apart; however, with offset for alternating rows, LVT\_FILLTIEHS cells can be placed every 40um apart with the exception of the top and bottom rows.

## Antenna Cells

The standard cell library contains 3 F\_DIODE cells: LVT\_F\_DIODEHS2, LVT\_F\_DIODEHS4 and LVT\_F\_DIODEHS8. The SMIC antenna effect prevention guideline within the "40nm LOGIC Antenna Ration Effect Generic Prevention Design Guide Rule" specifies the maximum length of wire allowed within the library. During place-and-route, the router may connect wires to the input gates of cells that are longer than the maximum length allowed. In this case, antenna cells can be placed on these inputs. Pin A on the antenna cell connects to two diodes, one reversed-biased from Pin A to ground and another from VDD to Pin A. The Antenna cells will need to be placed manually; fortunately, most place-and-route tools will indicate which nets will require the insertion of these cells.

# Standard Cell Datasheet

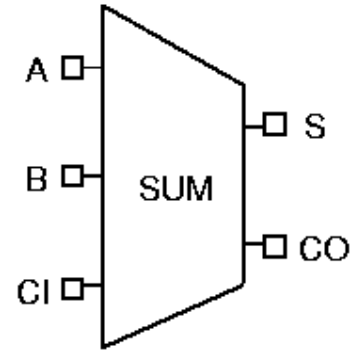
## LVT\_AD1HS

### Cell Description

1-Bit Full Adder

$CO = ((A \& B) | (A \& CI) | (B \& CI))$

$S = (A \wedge B \wedge CI)$



### Function Table

A	B	CI	CO	S
0	0	0	0	0
0	0	1	0	1
0	1	0	0	1
0	1	1	1	0
1	0	0	0	1
1	0	1	1	0
1	1	0	1	0
1	1	1	1	1

### Cell Size

CellName	Height(um)	Width(um)
LVT_AD1HSV1	1.26	5.04

### Pin Power (uW/MHz)

Pin	V1
A	0.00322
B	0.00259
CI	0.00107

### Pin Capacitance (pf)

Pin	V1
A	0.00126
B	0.00184
CI	0.00212

### Max Leakage Power (uW)

V1
0.01172992

### Delay Table (ns)

Description	V1
A→CO_FALL	0.07180
A→CO_RISE	0.06639
B→CO_FALL	0.06552
B→CO_RISE	0.05663
CI→CO_FALL	0.03828
CI→CO_RISE	0.03430
A→S_FALL	0.08817
A→S_RISE	0.08887
B→S_FALL	0.07081
B→S_RISE	0.07101
CI→S_FALL	0.03198
CI→S_RISE	0.03278



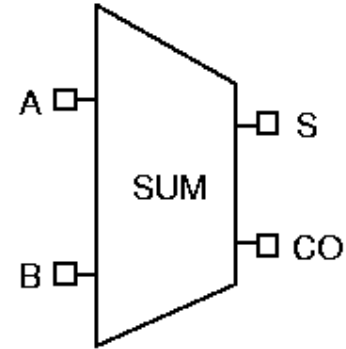
# LVT\_ADH1HS

## Cell Description

1-Bit Half Adder

$CO=(A\&B)$

$S=(A\wedge B)$



## Function Table

B	A	S	CO
0	0	0	0
0	1	1	0
1	0	1	0
1	1	0	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_ADH1HSV1	1.26	2.94

## Pin Power (uW/MHz)

Pin	V1
A	0.00165
B	0.00109

## Pin Capacitance (pf)

Pin	V1
A	0.00121
B	0.00186

## Max Leakage Power (uW)

V1
0.00914363

## Delay Table (ns)

Description	V1
A→CO_FALL	0.02158
A→CO_RISE	0.02689

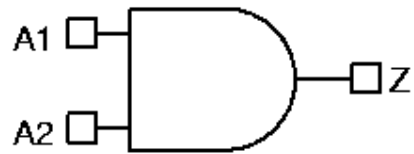
B→CO_FALL	0.02082
B→CO_RISE	0.02590
A→S_FALL	0.05370
A→S_RISE	0.05022
B→S_FALL	0.03408
B→S_RISE	0.03433

# LVT\_AND2HS

## Cell Description

2-Input AND

$Z=(A1\&A2)$



## Function Table

A1	A2	Z
0	X	0
1	0	0
1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_AND2HSV1	1.26	0.84
LVT_AND2HSV2	1.26	0.84
LVT_AND2HSV4	1.26	0.98
LVT_AND2HSV8	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2	V4	V8
A1	0.00064	0.00073	0.00112	0.00211
A2	0.00070	0.00079	0.00118	0.00221

## Pin Capacitance (pf)

Pin	V1	V2	V4	V8
A1	0.00051	0.00051	0.00050	0.00071
A2	0.00051	0.00051	0.00051	0.00072

## Max Leakage Power (uW)

V1	V2	V4	V8
0.00248399	0.00253799	0.00377153	0.01001899

## Delay Table (ns)

Description	V1	V2	V4	V8
-------------	----	----	----	----

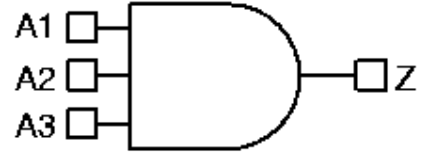
A1→Z_FALL	0.02554	0.02595	0.03073	0.02809
A1→Z_RISE	0.03125	0.03143	0.03640	0.03310
A2→Z_FALL	0.02778	0.02827	0.03275	0.02925
A2→Z_RISE	0.03368	0.03397	0.03884	0.03510

# LVT\_AND3HS

## Cell Description

3-Input AND

$Z=(A1\&A2\&A3)$



## Function Table

A1	A2	A3	Z
0	X	X	0
1	0	X	0
1	1	0	0
1	1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_AND3HSV1	1.26	0.98
LVT_AND3HSV2	1.26	0.98
LVT_AND3HSV4	1.26	1.12
LVT_AND3HSV8	1.26	1.54

## Pin Power (uW/MHz)

Pin	V1	V2	V4	V8
A1	0.00077	0.00086	0.00124	0.00234
A2	0.00084	0.00093	0.00132	0.00242
A3	0.00092	0.00101	0.00140	0.00252

## Pin Capacitance (pf)

Pin	V1	V2	V4	V8
A1	0.00055	0.00055	0.00054	0.00068
A2	0.00058	0.00057	0.00057	0.00072
A3	0.00058	0.00057	0.00058	0.00074

## Max Leakage Power (uW)

V1	V2	V4	V8
0.00353044	0.00357246	0.00484030	0.01201869

**Delay Table (ns)**

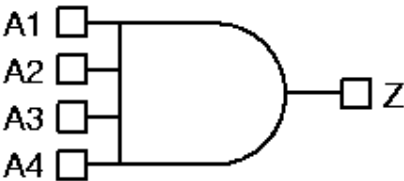
Description	V1	V2	V4	V8
A1→Z_FALL	0.02988	0.03022	0.03444	0.02951
A1→Z_RISE	0.03297	0.03259	0.03594	0.04570
A2→Z_FALL	0.03226	0.03221	0.03645	0.03027
A2→Z_RISE	0.03542	0.03492	0.03845	0.04828
A3→Z_FALL	0.03533	0.03510	0.03943	0.03200
A3→Z_RISE	0.03777	0.03721	0.04068	0.05051

# LVT\_AND4HS

## Cell Description

4-Input AND

$Z=(A1\&A2\&A3\&A4)$



## Function Table

A1	A2	A3	A4	Z
0	X	X	X	0
1	0	X	X	0
1	1	0	X	0
1	1	1	0	0
1	1	1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_AND4HSV1	1.26	1.12
LVT_AND4HSV2	1.26	1.12
LVT_AND4HSV4	1.26	1.26
LVT_AND4HSV8	1.26	1.68

## Pin Power (uW/MHz)

Pin	V1	V2	V4	V8
A1	0.00080	0.00090	0.00129	0.00253
A2	0.00089	0.00099	0.00138	0.00262
A3	0.00097	0.00107	0.00146	0.00270
A4	0.00106	0.00116	0.00156	0.00280

## Pin Capacitance (pf)

Pin	V1	V2	V4	V8
A1	0.00056	0.00056	0.00056	0.00068
A2	0.00061	0.00061	0.00061	0.00073
A3	0.00059	0.00058	0.00058	0.00070
A4	0.00060	0.00060	0.00060	0.00074

## Max Leakage Power (uW)

V1	V2	V4	V8
0.00437759	0.00447665	0.00569856	0.01484889

### Delay Table (ns)

Description	V1	V2	V4	V8
A1→Z_FALL	0.03123	0.03162	0.03579	0.03032
A1→Z_RISE	0.03672	0.03680	0.04035	0.05840
A2→Z_FALL	0.03429	0.03456	0.03828	0.03140
A2→Z_RISE	0.04098	0.04103	0.04462	0.06271
A3→Z_FALL	0.03673	0.03707	0.04056	0.03241
A3→Z_RISE	0.04336	0.04338	0.04681	0.06488
A4→Z_FALL	0.04005	0.04042	0.04386	0.03400
A4→Z_RISE	0.04605	0.04604	0.04951	0.06767

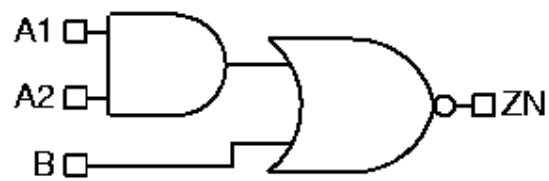


# LVT\_AOI21HS

## Cell Description

2-1 AOI

$$ZN = \neg((A1 \& A2) | B)$$



## Function Table

A1	A2	B	ZN
0	X	0	1
0	X	1	0
1	0	0	1
1	0	1	0
1	1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_AOI21HSV1	1.26	0.84
LVT_AOI21HSV2	1.26	0.84

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00042	0.00052
A2	0.00048	0.00060
B	0.00027	0.00034

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00056	0.00067
A2	0.00061	0.00074
B	0.00054	0.00065

## Max Leakage Power (uW)

V1	V2
0.00236669	0.00255267

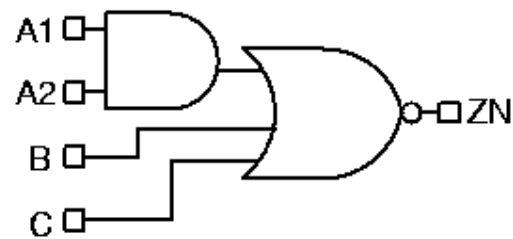
## Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.01612	0.01443
A1→ZN_RISE	0.02475	0.02171
A2→ZN_FALL	0.01742	0.01575
A2→ZN_RISE	0.02729	0.02443
B→ZN_FALL	0.00907	0.00821
B→ZN_RISE	0.01891	0.01664

# LVT\_AOI211HS

## Cell Description

2-1-1 AOI  
 $ZN = \neg((A1 \& A2) | B | C)$



## Function Table

A1	A2	B	C	ZN
0	X	0	0	1
0	X	0	1	0
0	X	1	X	0
1	0	0	0	1
1	0	0	1	0
1	0	1	X	0
1	1	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_AOI211HSV1	1.26	0.98
LVT_AOI211HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00054	0.00067
A2	0.00060	0.00076
B	0.00040	0.00050
C	0.00033	0.00040

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00055	0.00067
A2	0.00061	0.00075
B	0.00059	0.00071
C	0.00052	0.00063

## Max Leakage Power (uW)

V1	V2
0.00345774	0.00375070

### **Delay Table (ns)**

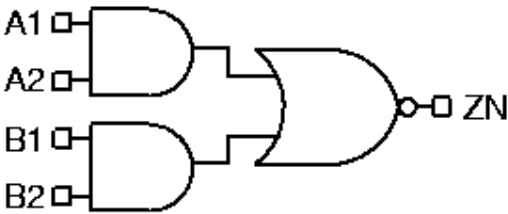
Description	V1	V2
A1→ZN_FALL	0.01790	0.01582
A1→ZN_RISE	0.04014	0.03490
A2→ZN_FALL	0.01924	0.01730
A2→ZN_RISE	0.04416	0.03939
B→ZN_FALL	0.01047	0.00951
B→ZN_RISE	0.03410	0.02994
C→ZN_FALL	0.00979	0.00878
C→ZN_RISE	0.03036	0.02589

# LVT\_AOI22HS

## Cell Description

2-2 AOI

$$ZN = \neg((A1 \& A2) | (B1 \& B2))$$



## Function Table

A1	A2	B1	B2	ZN
0	X	0	X	1
0	X	1	0	1
0	X	1	1	0
1	0	0	X	1
1	0	1	0	1
1	0	1	1	0
1	1	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_AOI22HSV1	1.26	0.98
LVT_AOI22HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00053	0.00067
A2	0.00059	0.00076
B1	0.00030	0.00037
B2	0.00035	0.00045

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00056	0.00067
A2	0.00061	0.00073
B1	0.00055	0.00066
B2	0.00054	0.00065

## Max Leakage Power (uW)

V1	V2
0.00274383	0.00391772

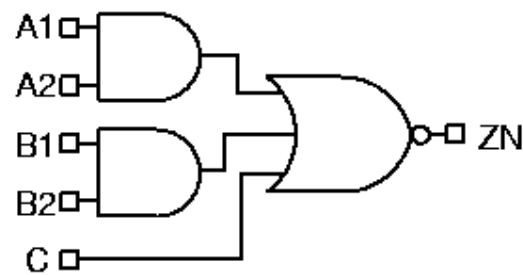
### **Delay Table (ns)**

Description	V1	V2
A1→ZN_FALL	0.01807	0.01640
A1→ZN_RISE	0.02684	0.02391
A2→ZN_FALL	0.01945	0.01792
A2→ZN_RISE	0.02953	0.02677
B1→ZN_FALL	0.01357	0.01217
B1→ZN_RISE	0.01901	0.01669
B2→ZN_FALL	0.01488	0.01350
B2→ZN_RISE	0.02170	0.01934

# LVT\_AOI221HS

## Cell Description

2-2-1 AOI  
$$ZN = \neg((A1 \& A2) | (B1 \& B2) | C)$$



## Function Table

A1	A2	B1	B2	C	ZN
0	X	0	X	0	1
0	X	0	X	1	0
0	X	1	0	0	1
0	X	1	0	1	0
0	X	1	1	X	0
1	0	0	X	0	1
1	0	0	X	1	0
1	0	1	0	0	1
1	0	1	0	1	0
1	0	1	1	X	0
1	1	X	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_AOI221HSV1	1.26	1.26
LVT_AOI221HSV2	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00069	0.00088
A2	0.00075	0.00096
B1	0.00050	0.00063
B2	0.00056	0.00071
C	0.00036	0.00045

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00057	0.00067
A2	0.00061	0.00073

B1	0.00056	0.00067
B2	0.00056	0.00067
C	0.00054	0.00065

### Max Leakage Power (uW)

V1	V2
0.00307180	0.00334228

### Delay Table (ns)

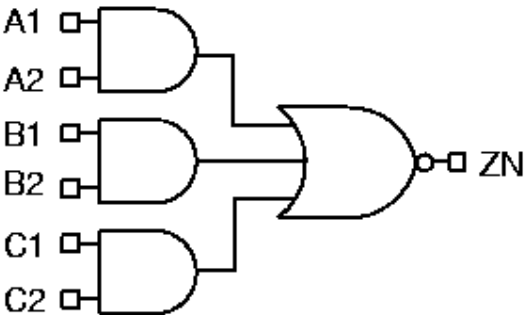
Description	V1	V2
A1→ZN_FALL	0.01945	0.01755
A1→ZN_RISE	0.04684	0.04210
A2→ZN_FALL	0.02079	0.01912
A2→ZN_RISE	0.05114	0.04679
B1→ZN_FALL	0.01776	0.01603
B1→ZN_RISE	0.04043	0.03606
B2→ZN_FALL	0.01943	0.01770
B2→ZN_RISE	0.04546	0.04104
C→ZN_FALL	0.01014	0.00928
C→ZN_RISE	0.03050	0.02693



# LVT\_AOI222HS

## Cell Description

2-2-2 AOI  
 $ZN = \neg((A1 \& A2) | (B1 \& B2) | (C1 \& C2))$



## Function Table

A1	A2	B1	B2	C1	C2	ZN
0	X	0	X	0	X	1
0	X	0	X	1	0	1
0	X	0	X	1	1	0
0	X	1	0	0	X	1
0	X	1	0	1	0	1
0	X	1	0	1	1	0
0	X	1	1	X	X	0
1	0	0	X	0	X	1
1	0	0	X	1	0	1
1	0	0	X	1	1	0
1	0	1	0	0	X	1
1	0	1	0	1	0	1
1	0	1	0	1	1	0
1	0	1	1	X	X	0
1	1	X	X	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_AOI222HSV1	1.26	1.54
LVT_AOI222HSV2	1.26	1.54

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00039	0.00048
A2	0.00044	0.00056
B1	0.00061	0.00077
B2	0.00067	0.00085
C1	0.00080	0.00101
C2	0.00086	0.00110

### Pin Capacitance (pf)

Pin	V1	V2
A1	0.00053	0.00063
A2	0.00052	0.00064
B1	0.00059	0.00070
B2	0.00055	0.00066
C1	0.00055	0.00066
C2	0.00060	0.00073

### Max Leakage Power (uW)

V1	V2
0.00320322	0.00348049

### Delay Table (ns)

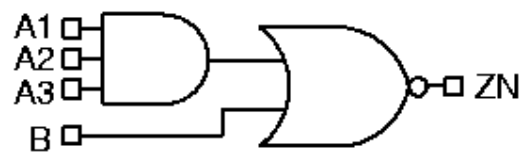
Description	V1	V2
A1→ZN_FALL	0.01561	0.01375
A1→ZN_RISE	0.03016	0.02615
A2→ZN_FALL	0.01652	0.01491
A2→ZN_RISE	0.03269	0.02916
B1→ZN_FALL	0.02015	0.01807
B1→ZN_RISE	0.04376	0.03888
B2→ZN_FALL	0.02156	0.01952
B2→ZN_RISE	0.04800	0.04325
C1→ZN_FALL	0.02175	0.01956
C1→ZN_RISE	0.04983	0.04464
C2→ZN_FALL	0.02317	0.02108
C2→ZN_RISE	0.05380	0.04891

# LVT\_AOI31HS

## Cell Description

3-1 AOI

$$ZN = \neg((A1 \& A2 \& A3) | B)$$



## Function Table

A1	A2	A3	B	ZN
0	X	X	0	1
0	X	X	1	0
1	0	X	0	1
1	0	X	1	0
1	1	0	0	1
1	1	0	1	0
1	1	1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_AOI31HSV1	1.26	0.98
LVT_AOI31HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00043	0.00053
A2	0.00049	0.00062
A3	0.00055	0.00069
B	0.00029	0.00035

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00058	0.00067
A2	0.00059	0.00070
A3	0.00061	0.00075
B	0.00054	0.00065

## Max Leakage Power (uW)

V1	V2
0.00234694	0.00288472

### Delay Table (ns)

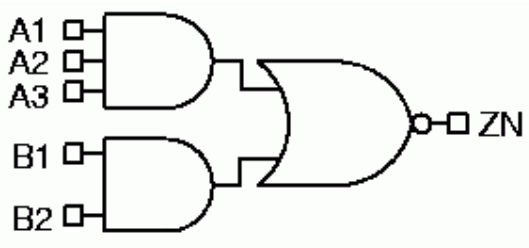
Description	V1	V2
A1→ZN_FALL	0.02239	0.01956
A1→ZN_RISE	0.02524	0.02179
A2→ZN_FALL	0.02467	0.02223
A2→ZN_RISE	0.02776	0.02466
A3→ZN_FALL	0.02576	0.02336
A3→ZN_RISE	0.03018	0.02697
B→ZN_FALL	0.00912	0.00816
B→ZN_RISE	0.01845	0.01599

# LVT\_AOI32HS

## Cell Description

3-2 AOI

$$ZN = \neg((A1 \& A2 \& A3) | (B1 \& B2))$$



## Function Table

A1	A2	A3	B1	B2	ZN
0	X	X	0	X	1
0	X	X	1	0	1
0	X	X	1	1	0
1	0	X	0	X	1
1	0	X	1	0	1
1	0	X	1	1	0
1	1	0	0	X	1
1	1	0	1	0	1
1	1	0	1	1	0
1	1	1	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_AOI32HSV1	1.26	1.12
LVT_AOI32HSV2	1.26	1.12

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00053	0.00067
A2	0.00059	0.00076
A3	0.00064	0.00083
B1	0.00031	0.00039
B2	0.00038	0.00048

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00056	0.00067
A2	0.00063	0.00076
A3	0.00062	0.00074

B1	0.00055	0.00069
B2	0.00054	0.00063

### Max Leakage Power (uW)

V1	V2
0.00268393	0.00402434

### Delay Table (ns)

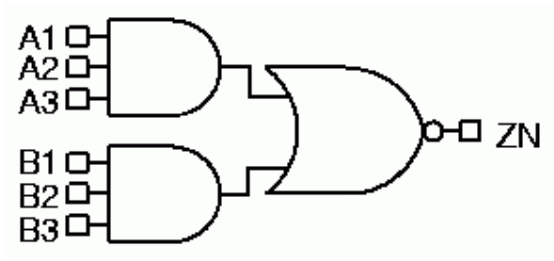
Description	V1	V2
A1→ZN_FALL	0.02498	0.02248
A1→ZN_RISE	0.02674	0.02378
A2→ZN_FALL	0.02769	0.02551
A2→ZN_RISE	0.02946	0.02668
A3→ZN_FALL	0.02877	0.02656
A3→ZN_RISE	0.03200	0.02905
B1→ZN_FALL	0.01360	0.01213
B1→ZN_RISE	0.01853	0.01625
B2→ZN_FALL	0.01526	0.01370
B2→ZN_RISE	0.02145	0.01891

# LVT\_AOI33HS

## Cell Description

3-3 AOI

$$ZN = \neg((A1 \& A2 \& A3) | (B1 \& B2 \& B3))$$



## Function Table

A1	A2	A3	B1	B2	B3	ZN
0	X	X	0	X	X	1
0	X	X	1	0	X	1
0	X	X	1	1	0	1
0	X	X	1	1	1	0
1	0	X	0	X	X	1
1	0	X	1	0	X	1
1	0	X	1	1	0	1
1	0	X	1	1	1	0
1	1	0	0	X	X	1
1	1	0	1	0	X	1
1	1	0	1	1	0	1
1	1	0	1	1	1	0
1	1	1	X	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_AOI33HSV1	1.26	1.40
LVT_AOI33HSV2	1.26	1.40

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00065	0.00082
A2	0.00071	0.00090
A3	0.00077	0.00098
B1	0.00040	0.00049
B2	0.00047	0.00059
B3	0.00053	0.00067

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00057	0.00068
A2	0.00064	0.00070
A3	0.00060	0.00073
B1	0.00054	0.00065
B2	0.00054	0.00065
B3	0.00054	0.00065

### Max Leakage Power (uW)

V1	V2
0.00459800	0.00653072

### Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.02920	0.02640
A1→ZN_RISE	0.02922	0.02600
A2→ZN_FALL	0.03175	0.02897
A2→ZN_RISE	0.03160	0.02843
A3→ZN_FALL	0.03276	0.03008
A3→ZN_RISE	0.03369	0.03051
B1→ZN_FALL	0.02054	0.01803
B1→ZN_RISE	0.02086	0.01825
B2→ZN_FALL	0.02379	0.02132
B2→ZN_RISE	0.02381	0.02116
B3→ZN_FALL	0.02500	0.02248
B3→ZN_RISE	0.02606	0.02332

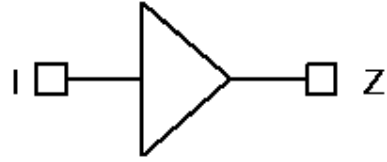


# LVT\_BUFHS

## Cell Description

Non-Inverting Buffer

$Z=I$



## Function Table

I	Z
0	0
1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_BUFHSV1	1.26	0.56
LVT_BUFHSV2	1.26	0.56
LVT_BUFHSV3	1.26	0.84
LVT_BUFHSV4	1.26	0.84
LVT_BUFHSV6	1.26	0.98
LVT_BUFHSV8	1.26	1.26
LVT_BUFHSV12	1.26	1.82
LVT_BUFHSV16	1.26	2.24
LVT_BUFHSV20	1.26	2.80
LVT_BUFHSV24	1.26	3.36

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
I	0.00062	0.00072	0.00095	0.00113	0.00163	0.00205	0.00309	0.00403

Pin	V20	V24
I	0.00498	0.00602

## Pin Capacitance (pf)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
I	0.00053	0.00053	0.00058	0.00063	0.00074	0.00123	0.00172	0.00200

Pin	V20	V24
I	0.00267	0.00331

### Max Leakage Power (uW)

V1	V2	V3	V4	V6	V8	V12	V16
0.00149061	0.00163288	0.00376993	0.00453275	0.00706404	0.01083884	0.01836302	0.02542359

V20	V24
0.03380040	0.04152418

### Delay Table (ns)

Description	V1	V2	V3	V4	V6	V8	V12	V16
I→Z_FALL	0.02549	0.02620	0.02439	0.02290	0.02465	0.02017	0.02019	0.02068
I→Z_RISE	0.02302	0.02286	0.02050	0.01976	0.02052	0.01742	0.01716	0.01738

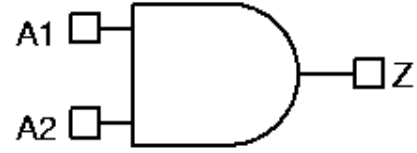
Description	V20	V24
I→Z_FALL	0.01963	0.01945
I→Z_RISE	0.01665	0.01657

# LVT\_CLKAND2HS

## Cell Description

2-Input Clock AND

$Z=(A1\&A2)$



## Function Table

A1	A2	Z
0	X	0
1	0	0
1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_CLKAND2HSV1	1.26	0.84
LVT_CLKAND2HSV2	1.26	0.84
LVT_CLKAND2HSV4	1.26	1.12
LVT_CLKAND2HSV8	1.26	1.68

## Pin Power (uW/MHz)

Pin	V1	V2	V4	V8
A1	0.00066	0.00076	0.00143	0.00297
A2	0.00076	0.00086	0.00153	0.00307

## Pin Capacitance (pf)

Pin	V1	V2	V4	V8
A1	0.00061	0.00059	0.00058	0.00059
A2	0.00059	0.00060	0.00059	0.00059

## Max Leakage Power (uW)

V1	V2	V4	V8
0.00238998	0.00281620	0.00665239	0.01487073

## Delay Table (ns)

Description	V1	V2	V4	V8
-------------	----	----	----	----

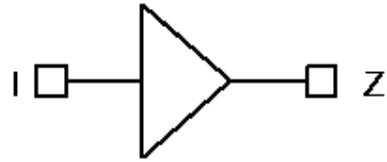
A1→Z_FALL	0.02748	0.02797	0.03797	0.05629
A1→Z_RISE	0.02255	0.02216	0.02523	0.03504
A2→Z_FALL	0.03113	0.03177	0.04116	0.05895
A2→Z_RISE	0.02464	0.02421	0.02721	0.03699

# LVT\_CLKBUFHS

## Cell Description

Clock Buffer with Balanced Rise/Fall Time

Z=I



## Function Table

I	Z
0	0
1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_CLKBUFHSV1	1.26	0.56
LVT_CLKBUFHSV2	1.26	0.56
LVT_CLKBUFHSV3	1.26	0.84
LVT_CLKBUFHSV4	1.26	0.84
LVT_CLKBUFHSV6	1.26	0.98
LVT_CLKBUFHSV8	1.26	1.26
LVT_CLKBUFHSV12	1.26	1.68
LVT_CLKBUFHSV16	1.26	2.24
LVT_CLKBUFHSV20	1.26	2.80
LVT_CLKBUFHSV24	1.26	3.08

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
I	0.00062	0.00070	0.00094	0.00111	0.00153	0.00185	0.00270	0.00349

Pin	V20	V24
I	0.00455	0.00525

## Pin Capacitance (pf)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
I	0.00053	0.00053	0.00062	0.00068	0.00070	0.00101	0.00130	0.00170

Pin	V20	V24
I	0.00225	0.00245

### Max Leakage Power (uW)

V1	V2	V3	V4	V6	V8	V12	V16
0.00145588	0.00164282	0.00416781	0.00501393	0.00723452	0.00968382	0.01757344	0.02296167

V20	V24
0.03024714	0.03703531

### Delay Table (ns)

Description	V1	V2	V3	V4	V6	V8	V12	V16
I→Z_FALL	0.02628	0.02665	0.02228	0.02120	0.02428	0.02176	0.02128	0.02120
I→Z_RISE	0.02285	0.02242	0.02039	0.01871	0.02192	0.01994	0.01960	0.02071

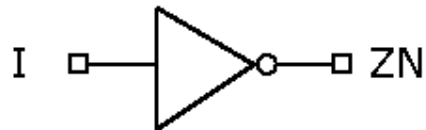
Description	V20	V24
I→Z_FALL	0.02074	0.02138
I→Z_RISE	0.02047	0.02042

# LVT\_CLKNHS

## Cell Description

Inverting Clock Buffer with Balanced Rise/Fall Time

ZN=(!I)



## Function Table

I	ZN
0	1
1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_CLKNHSV1	1.26	0.42
LVT_CLKNHSV2	1.26	0.42
LVT_CLKNHSV3	1.26	0.56
LVT_CLKNHSV4	1.26	0.56
LVT_CLKNHSV6	1.26	0.84
LVT_CLKNHSV8	1.26	0.98
LVT_CLKNHSV12	1.26	1.26
LVT_CLKNHSV16	1.26	1.68
LVT_CLKNHSV20	1.26	2.10
LVT_CLKNHSV24	1.26	2.38

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
I	0.00020	0.00024	0.00030	0.00033	0.00057	0.00065	0.00095	0.00121

Pin	V20	V24
I	0.00150	0.00185

## Pin Capacitance (pf)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
I	0.00057	0.00067	0.00105	0.00120	0.00173	0.00218	0.00331	0.00438

Pin	V20	V24
I	0.00541	0.00649

### Max Leakage Power (uW)

V1	V2	V3	V4	V6	V8	V12	V16
0.00094292	0.00116272	0.00212648	0.00253653	0.00561979	0.00761807	0.01258146	0.01931775

V20	V24
0.02521548	0.03156305

### Delay Table (ns)

Description	V1	V2	V3	V4	V6	V8	V12	V16
I→ZN_FALL	0.00914	0.00829	0.00681	0.00651	0.00643	0.00631	0.00610	0.00586
I→ZN_RISE	0.01111	0.00974	0.00804	0.00746	0.00721	0.00650	0.00624	0.00604

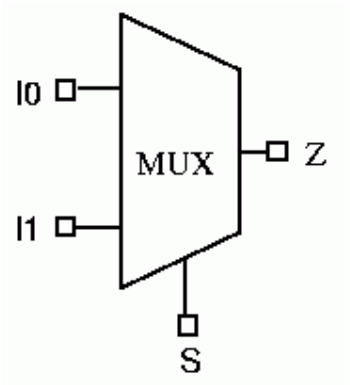
Description	V20	V24
I→ZN_FALL	0.00596	0.00618
I→ZN_RISE	0.00623	0.00641



# LVT\_CKMUX2HS

## Cell Description

2-to-1 Multiplexer  
 $Z=((I0\&(!S))|(I1\&S))$



## Function Table

S	I0	I1	Z
0	0	X	0
0	1	X	1
1	X	0	0
1	X	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_CKMUX2HSV1	1.26	1.82
LVT_CKMUX2HSV2	1.26	1.82

## Pin Power (uW/MHz)

Pin	V1	V2
I0	0.00105	0.00113
I1	0.00110	0.00118
S	0.00114	0.00122

## Pin Capacitance (pf)

Pin	V1	V2
I0	0.00063	0.00063
I1	0.00065	0.00065
S	0.00102	0.00106

## Max Leakage Power (uW)

V1	V2
0.00548702	0.00567911

## Delay Table (ns)

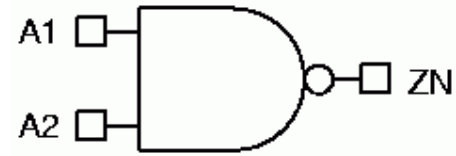
Description	V1	V2
I0→Z_FALL	0.04040	0.04001
I0→Z_RISE	0.03125	0.03093
I1→Z_FALL	0.04312	0.04269
I1→Z_RISE	0.03128	0.03096
S→Z_FALL	0.03405	0.03392
S→Z_RISE	0.03059	0.03043

# LVT\_CLKNAND2HS

## Cell Description

2-Input NAND

$ZN = \neg(A1 \& A2)$



## Function Table

A1	A2	ZN
0	X	1
1	0	1
1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_CLKNAND2HSV1	1.26	0.56
LVT_CLKNAND2HSV2	1.26	0.56
LVT_CLKNAND2HSV3	1.26	0.98
LVT_CLKNAND2HSV4	1.26	0.98
LVT_CLKNAND2HSV8	1.26	1.68

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V4	V8
A1	0.00027	0.00031	0.00042	0.00057	0.00103
A2	0.00034	0.00039	0.00062	0.00081	0.00148

## Pin Capacitance (pf)

Pin	V1	V2	V3	V4	V8
A1	0.00060	0.00068	0.00100	0.00119	0.00226
A2	0.00064	0.00072	0.00102	0.00121	0.00234

## Max Leakage Power (uW)

V1	V2	V3	V4	V8
0.00191825	0.00257743	0.00600634	0.00751379	0.01907642

## Delay Table (ns)

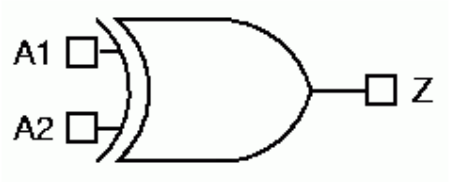
Description	V1	V2	V3	V4	V8
A1→ZN_FALL	0.01160	0.01155	0.01012	0.01004	0.00898
A1→ZN_RISE	0.01242	0.01071	0.00904	0.00895	0.00793
A2→ZN_FALL	0.01265	0.01275	0.01247	0.01234	0.01105
A2→ZN_RISE	0.01367	0.01181	0.01074	0.01053	0.00940

# LVT\_CLKXOR2HS

## Cell Description

2-Input Exclusive OR

$$Z=(A1\wedge A2)$$



## Function Table

A2	A1	Z
0	0	0
0	1	1
1	0	1
1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_CLKXOR2HSV1	1.26	1.96
LVT_CLKXOR2HSV2	1.26	1.96

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00120	0.00128
A2	0.00202	0.00211

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00120	0.00120
A2	0.00072	0.00071

## Max Leakage Power (uW)

V1	V2
0.00517060	0.00514396

## Delay Table (ns)

Description	V1	V2
A1→Z_FALL	0.03258	0.03288

A1→Z_RISE	0.03139	0.03087
A2→Z_FALL	0.05220	0.05285
A2→Z_RISE	0.04537	0.04506

# LVT\_CLKLANQHS

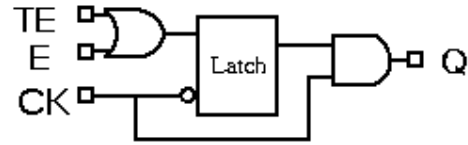
## Cell Description

pre-controlled positiveedge triggered clock-gating latch for

Low Power Design

$IQ = !CK \ ? \ (TE|E)$

$Q = IQ \& CK$



## Function Table

CK<1>	CK	TE	E	Q
0	1	0	0	0
0	1	0	1	1
0	1	1	X	1
0	0	X	X	0
1	1	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_CLKLANQHSV1	1.26	2.94
LVT_CLKLANQHSV2	1.26	2.94
LVT_CLKLANQHSV3	1.26	3.08
LVT_CLKLANQHSV4	1.26	3.08
LVT_CLKLANQHSV6	1.26	3.36
LVT_CLKLANQHSV8	1.26	3.50
LVT_CLKLANQHSV12	1.26	3.92
LVT_CLKLANQHSV16	1.26	4.06
LVT_CLKLANQHSV20	1.26	4.48
LVT_CLKLANQHSV24	1.26	4.90

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
CK	0.00138	0.00139	0.00137	0.00136	0.00136	0.00138	0.00136	0.00138
E	0.00033	0.00033	0.00032	0.00032	0.00032	0.00033	0.00032	0.00032
Q	0.00113	0.00125	0.00143	0.00158	0.00205	0.00253	0.00370	0.00504
TE	0.00036	0.00036	0.00035	0.00035	0.00036	0.00036	0.00036	0.00036

Pin	V20	V24
CK	0.00138	0.00137
E	0.00032	0.00033
Q	0.00664	0.00857

TE	0.00036	0.00036
----	---------	---------

### Pin Capacitance (pf)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
CK	0.00052	0.00053	0.00053	0.00054	0.00051	0.00052	0.00050	0.00052
E	0.00055	0.00055	0.00055	0.00055	0.00055	0.00055	0.00055	0.00056
TE	0.00054	0.00054	0.00054	0.00054	0.00056	0.00056	0.00056	0.00057

Pin	V20	V24
CK	0.00052	0.00053
E	0.00056	0.00056
TE	0.00057	0.00056

### Max Leakage Power (uW)

V1	V2	V3	V4	V6	V8	V12	V16
0.00719259	0.00757311	0.00859963	0.00907673	0.01082110	0.01341251	0.01930878	0.02501019

V20	V24
0.03133542	0.03816639

### Delay Table (ns)

Description	V1	V2	V3	V4	V6	V8	V12	V16
CK→Q_FALL	0.06091	0.06085	0.06096	0.06219	0.06533	0.06826	0.07474	0.08414
CK→Q_RISE	0.06174	0.06161	0.06160	0.06255	0.06580	0.07086	0.07904	0.08862

Description	V20	V24
CK→Q_FALL	0.09126	0.09624
CK→Q_RISE	0.09726	0.10507

### Timing Constraints (ns)

Pin	Requirement	V1	V2	V3	V4	V6	V8
E	hold_FALL→CK	-0.03149	-0.02862	-0.02861	-0.02861	-0.02861	-0.02861
E	hold_RISE→CK	-0.01431	-0.01431	-0.01432	-0.01432	-0.01431	-0.01431
E	setup_FALL→CK	0.03436	0.03434	0.03434	0.03436	0.03721	0.03721
E	setup_RISE→CK	0.01718	0.01718	0.01720	0.01718	0.01717	0.01719
TE	hold_FALL→CK	-0.03434	-0.03149	-0.03149	-0.03148	-0.03149	-0.03149
TE	hold_RISE→CK	-0.01432	-0.01432	-0.01432	-0.01432	-0.01431	-0.01432
TE	setup_FALL→CK	0.03721	0.03722	0.03722	0.03720	0.04008	0.04008
TE	setup_RISE→CK	0.01717	0.02004	0.02005	0.02005	0.02004	0.02004
CK	minpwl	0.06103	0.06102	0.06103	0.06105	0.06104	0.06264

Pin	Requirement	V12	V16	V20	V24
E	hold_FALL→CK	-0.02575	-0.02289	-0.02289	-0.02861



E	hold_RISE→CK	-0.01432	-0.02578	-0.02578	-0.01432
E	setup_FALL→CK	0.03435	0.03148	0.03148	0.03722
E	setup_RISE→CK	0.01720	0.03149	0.03149	0.01719
TE	hold_FALL→CK	-0.02864	-0.02576	-0.02576	-0.03149
TE	hold_RISE→CK	-0.01432	-0.02864	-0.02864	-0.01432
TE	setup_FALL→CK	0.03721	0.03721	0.03722	0.04008
TE	setup_RISE→CK	0.02006	0.03436	0.03436	0.02004
CK	minpwl	0.06104	0.06901	0.07057	0.06420

# LVT\_DELHS

## Cell Description

Delay cell

$Z=I$



## Function Table

I	Z
0	0
1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_DELHS2	1.26	1.54

## Pin Power (uW/MHz)

Pin	LVT_DELHS2
I	0.00181

## Pin Capacitance (pf)

Pin	LVT_DELHS2
I	0.00050

## Max Leakage Power (uW)

LVT_DELHS2
0.00212140

## Delay Table (ns)

Description	LVT_DELHS2
I→Z_FALL	0.09654
I→Z_RISE	0.09597

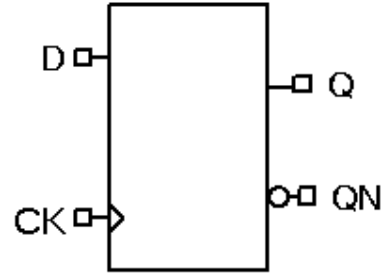
# LVT\_DHS

## Cell Description

D Flip-Flop

Q = rising (CK) ? D : pre\_Q

QN = !Q



## Function Table

CK<1>	CK	D	Q
0	0	X	Q<1>
0	1	0	0
0	1	1	1
1	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_DHSV1	1.26	3.22
LVT_DHSV2	1.26	3.22

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00141	0.00141
D	0.00052	0.00052
Q	0.00092	0.00103
QN	0.00093	0.00104

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00047	0.00047
D	0.00056	0.00056

## Max Leakage Power (uW)

V1	V2
0.00597979	0.00671760

## Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.08354	0.08367
CK→Q_RISE	0.08167	0.08282
CK→QN_FALL	0.06259	0.06167
CK→QN_RISE	0.06578	0.06478

### Timing Constraints (ns)

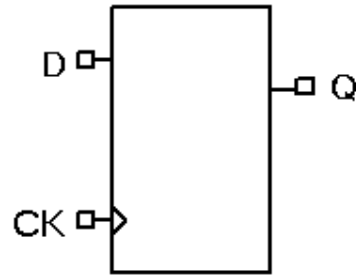
Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.00000	0.00287
D	hold_RISE→CK	-0.00573	-0.00573
D	setup_FALL→CK	0.01432	0.01432
D	setup_RISE→CK	0.01146	0.01433
CK	minpwh	0.06501	0.06822
CK	minpwl	0.06975	0.06975

# LVT\_DQHS

## Cell Description

D Flip-Flop, Single Output

Q = rising (CK) ? D : pre\_Q



## Function Table

CK<1>	CK	D	Q
0	0	X	Q<1>
0	1	0	0
0	1	1	1
1	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_DQHVS1	1.26	2.94
LVT_DQHVS2	1.26	2.94

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00136	0.00136
D	0.00051	0.00052
Q	0.00141	0.00151

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00048	0.00048
D	0.00059	0.00060

## Max Leakage Power (uW)

V1	V2
0.00529539	0.00541182

## Delay Table (ns)

Description	V1	V2
-------------	----	----

CK→Q_FALL	0.07396	0.07357
CK→Q_RISE	0.07095	0.07066

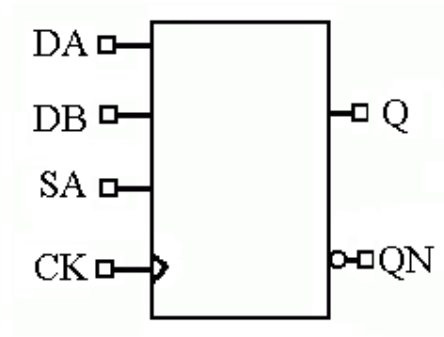
### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.00000	-0.00000
D	hold_RISE→CK	-0.00287	-0.00287
D	setup_FALL→CK	0.01430	0.01430
D	setup_RISE→CK	0.01145	0.01145
CK	minpwh	0.04598	0.04598
CK	minpwl	0.06580	0.06581

# LVT\_DXHS

## Cell Description

D Flip-Flop with Mux Inputs  
Q = rising (CK) ? (DA&SA|DB&!SA) : pre\_Q  
QN = !Q



## Function Table

CK<1>	CK	SA	DB	DA	Q
0	0	X	X	X	Q<1>
0	1	0	0	X	0
0	1	0	1	X	1
0	1	1	X	0	0
0	1	1	X	1	1
1	X	X	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_DXHSV1	1.26	4.20
LVT_DXHSV2	1.26	4.20

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00155	0.00156
DA	0.00038	0.00038
DB	0.00034	0.00034
Q	0.00093	0.00103
QN	0.00094	0.00104
SA	0.00068	0.00068

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00047	0.00047
DA	0.00042	0.00042
DB	0.00049	0.00050
SA	0.00098	0.00098

### Max Leakage Power (uW)

V1	V2
0.00684949	0.00713958

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.08535	0.08605
CK→Q_RISE	0.08399	0.08611
CK→QN_FALL	0.06391	0.06475
CK→QN_RISE	0.07043	0.06944

### Timing Constraints (ns)

Pin	Requirement	V1	V2
DA	hold_FALL→CK	-0.01718	-0.01431
DA	hold_RISE→CK	-0.02864	-0.02864
DA	setup_FALL→CK	0.04294	0.04293
DA	setup_RISE→CK	0.04296	0.04580
DB	hold_FALL→CK	-0.01144	-0.00858
DB	hold_RISE→CK	-0.02577	-0.02577
DB	setup_FALL→CK	0.04007	0.04008
DB	setup_RISE→CK	0.03722	0.04009
SA	hold_FALL→CK	-0.04006	-0.04008
SA	hold_RISE→CK	-0.03148	-0.02575
SA	setup_FALL→CK	0.05439	0.05439
SA	setup_RISE→CK	0.06012	0.06012
CK	minpwh	0.06822	0.07142
CK	minpwl	0.08171	0.08171



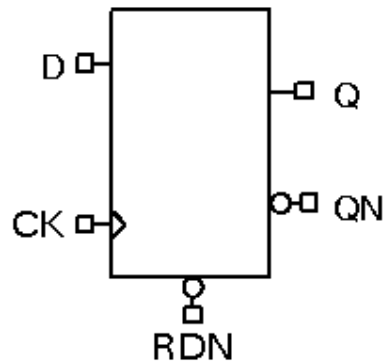
# LVT\_DRNHS

## Cell Description

D Flip-Flop with Async Clear

Q = !RDN ? 0 : rising (CK) ? D : pre\_Q

QN = !Q



## Function Table

RDN	CK<1>	CK	D	Q
0	X	X	X	0
1	0	0	X	Q<1>
1	0	1	0	0
1	0	1	1	1
1	1	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_DRNHSV1	1.26	3.78
LVT_DRNHSV2	1.26	3.78

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00143	0.00143
D	0.00030	0.00030
Q	0.00119	0.00128
QN	0.00123	0.00133
RDN	0.00034	0.00034

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00046	0.00046
D	0.00044	0.00045
RDN	0.00167	0.00167

## Max Leakage Power (uW)

V1	V2
0.00914844	0.00962504

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.08229	0.08314
CK→Q_RISE	0.09217	0.09343
RDN→Q_FALL	0.02448	0.02429
CK→QN_FALL	0.06190	0.06233
CK→QN_RISE	0.06520	0.06407
RDN→QN_RISE	0.07405	0.07419

### Timing Constraints (ns)

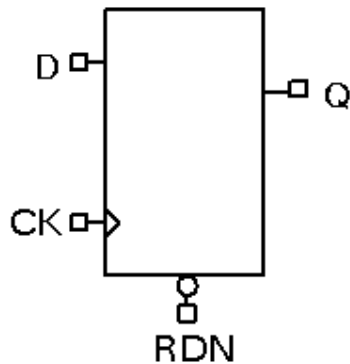
Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.00287	-0.00000
D	hold_RISE→CK	-0.01430	-0.01431
D	setup_FALL→CK	0.02575	0.02290
D	setup_RISE→CK	0.02290	0.02577
RDN	setup_RISE→CK	0.02576	0.02576
RDN	hold_RISE→CK	-0.02004	-0.02004
CK	minpwh	0.06507	0.07141
CK	minpwl	0.07378	0.07378
RDN	minpwl	0.04599	0.04916

# LVT\_DRNQHS

## Cell Description

D Flip-Flop with Async Clear, Single Output

Q = !RDN ? 0 : rising (CK) ? D : pre\_Q



## Function Table

RDN	CK<1>	CK	D	Q
0	X	X	X	0
1	0	0	X	Q<1>
1	0	1	0	0
1	0	1	1	1
1	1	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_DRNQHSV1	1.26	3.50
LVT_DRNQHSV2	1.26	3.50

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00145	0.00144
D	0.00029	0.00029
Q	0.00185	0.00194
RDN	0.00034	0.00034

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00047	0.00047
D	0.00044	0.00044
RDN	0.00162	0.00163

## Max Leakage Power (uW)

V1	V2
0.00745198	0.00765091

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.07810	0.07802
CK→Q_RISE	0.07536	0.07495
RDN→Q_FALL	0.02965	0.02972

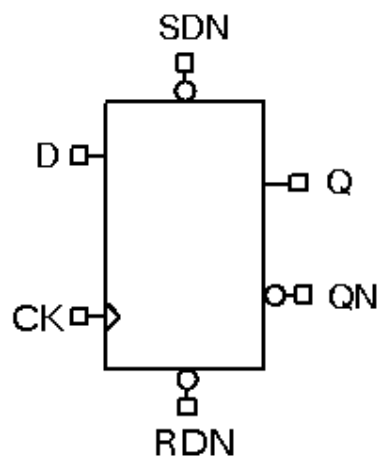
### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.00574	-0.00574
D	hold_RISE→CK	-0.01431	-0.01431
D	setup_FALL→CK	0.02290	0.02290
D	setup_RISE→CK	0.02289	0.02289
RDN	setup_RISE→CK	0.02289	0.02576
RDN	hold_RISE→CK	-0.02004	-0.02004
CK	minpwh	0.04600	0.04600
CK	minpwl	0.07378	0.07378
RDN	minpwl	0.04601	0.04918

# LVT\_DRSNHS

## Cell Description

D Flip-Flop with Async Clear and Set  
 $Q = !SDN ? 1 : !RDN ? 0 : \text{rising}(CK) ? D : \text{pre\_}Q$   
 $QN = !Q$



## Function Table

RDN	SDN	CK<1>	CK	D	Q
0	0	X	X	X	1
0	1	X	X	X	0
1	0	X	X	X	1
1	1	0	0	X	Q<1>
1	1	0	1	0	0
1	1	0	1	1	1
1	1	1	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_DRSNHSV1	1.26	5.88
LVT_DRSNHSV2	1.26	5.88

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00208	0.00208
D	0.00030	0.00030
Q	0.00136	0.00146
QN	0.00137	0.00147
RDN	0.00101	0.00101
SDN	0.00018	0.00018

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00065	0.00065
D	0.00047	0.00047
RDN	0.00117	0.00117
SDN	0.00088	0.00088

### Max Leakage Power (uW)

V1	V2
0.00725554	0.00769425

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.10898	0.11036
CK→Q_RISE	0.10050	0.10195
RDN→Q_FALL	0.09782	0.09923
SDN→Q_FALL	0.06951	0.07096
SDN→Q_RISE	0.06903	0.06985
CK→QN_FALL	0.08253	0.08203
CK→QN_RISE	0.09054	0.08894
RDN→QN_RISE	0.07907	0.07753
SDN→QN_FALL	0.05148	0.05049
SDN→QN_RISE	0.05076	0.04923

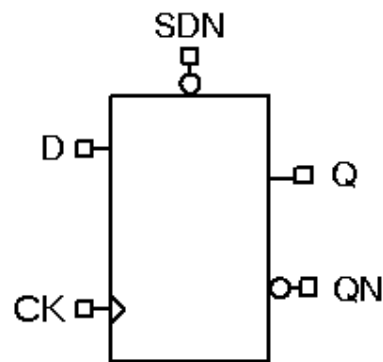
### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.00574	-0.00287
D	hold_RISE→CK	-0.02863	-0.02577
D	setup_FALL→CK	0.03435	0.03435
D	setup_RISE→CK	0.04294	0.04581
RDN	setup_RISE→CK	0.04293	0.04579
RDN	hold_RISE→CK	-0.03720	-0.03721
SDN	setup_RISE→CK	-0.04866	-0.04580
SDN	hold_RISE→CK	0.06298	0.06297
SDN	non_seq_hold_RISE→RDN	-0.03434	-0.03434
SDN	non_seq_setup_RISE→RDN	0.04008	0.04581
CK	minpwh	0.08409	0.09042
CK	minpwl	0.11345	0.11345
RDN	minpwl	0.06818	0.07140
SDN	minpwl	0.08404	0.09039

# LVT\_DSNHS

## Cell Description

D Flip-Flop with Async Set  
Q = !SDN ? 1 : rising (CK) ? D : pre\_Q  
QN = !Q



## Function Table

SDN	CK<l>	CK	D	Q
0	X	X	X	1
1	0	0	X	Q<l>
1	0	1	0	0
1	0	1	1	1
1	1	X	X	Q<l>

## Cell Size

CellName	Height(um)	Width(um)
LVT_DSNHSV1	1.26	3.64
LVT_DSNHSV2	1.26	3.64

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00151	0.00151
D	0.00041	0.00041
Q	0.00124	0.00134
QN	0.00120	0.00128
SDN	0.00014	0.00014

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00048	0.00048
D	0.00052	0.00052
SDN	0.00105	0.00105

## Max Leakage Power (uW)

V1	V2
0.00752625	0.00797839

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.09081	0.09234
CK→Q_RISE	0.08868	0.08933
SDN→Q_RISE	0.06208	0.06272
CK→QN_FALL	0.07061	0.07093
CK→QN_RISE	0.07412	0.07336
SDN→QN_FALL	0.04560	0.04595

### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.00000	0.00286
D	hold_RISE→CK	-0.01145	-0.01145
D	setup_FALL→CK	0.02003	0.02003
D	setup_RISE→CK	0.02291	0.02291
SDN	setup_RISE→CK	-0.03149	-0.03149
SDN	hold_RISE→CK	0.04007	0.04007
CK	minpwh	0.07771	0.08407
CK	minpwl	0.07770	0.07770
SDN	minpwl	0.07454	0.08088

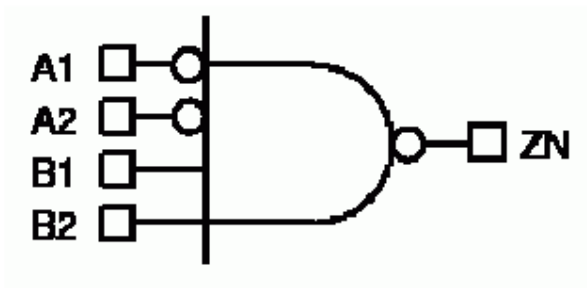


# LVT\_I2NAND4HS

## Cell Description

4-Input NAND with 2 Inverted Inputs

$$Z_N = \neg((\neg A_1) \& (\neg A_2) \& B_1 \& B_2)$$



## Function Table

A1	A2	B1	B2	ZN
0	0	0	X	1
0	0	1	0	1
0	0	1	1	0
0	1	X	X	1
1	X	X	X	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_I2NAND4HSV1	1.26	1.54
LVT_I2NAND4HSV2	1.26	1.54

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00090	0.00097
A2	0.00090	0.00097
B1	0.00054	0.00059
B2	0.00062	0.00067

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00052	0.00052
A2	0.00052	0.00052
B1	0.00060	0.00065
B2	0.00061	0.00066

## Max Leakage Power (uW)

V1	V2
0.00706466	0.00885360

**Delay Table (ns)**

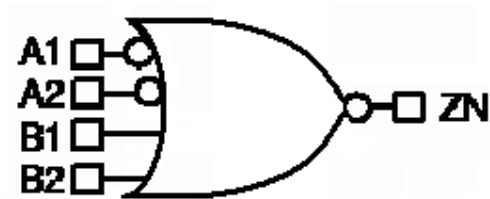
Description	V1	V2
A1→ZN_FALL	0.03943	0.04174
A1→ZN_RISE	0.02881	0.02723
A2→ZN_FALL	0.04229	0.04481
A2→ZN_RISE	0.02884	0.02712
B1→ZN_FALL	0.02648	0.02826
B1→ZN_RISE	0.01681	0.01424
B2→ZN_FALL	0.02794	0.02978
B2→ZN_RISE	0.01827	0.01528

# LVT\_I2NOR4HS

## Cell Description

4-Input NOR with 2 Inverted Inputs

$$ZN = ((\neg A1) \vee (\neg A2) \vee B1 \vee B2)$$



## Function Table

A1	A2	B1	B2	ZN
0	X	X	X	0
1	0	X	X	0
1	1	0	0	1
1	1	0	1	0
1	1	1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_I2NOR4HSV1	1.26	1.54
LVT_I2NOR4HSV2	1.26	1.54

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00109	0.00115
A2	0.00101	0.00108
B1	0.00047	0.00052
B2	0.00037	0.00042

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00051	0.00051
A2	0.00051	0.00050
B1	0.00060	0.00066
B2	0.00057	0.00062

## Max Leakage Power (uW)

V1	V2
0.00564795	0.00515887

**Delay Table (ns)**

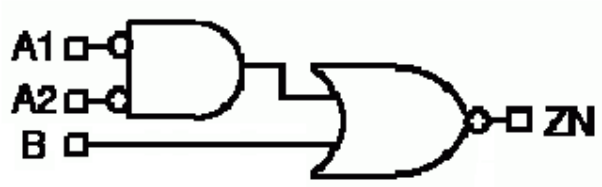
Description	V1	V2
A1→ZN_FALL	0.03243	0.03092
A1→ZN_RISE	0.05683	0.06056
A2→ZN_FALL	0.03101	0.02960
A2→ZN_RISE	0.05423	0.05828
B1→ZN_FALL	0.01165	0.00999
B1→ZN_RISE	0.03756	0.04109
B2→ZN_FALL	0.01075	0.00942
B2→ZN_RISE	0.03120	0.03481

# LVT\_IAO21HS

## Cell Description

2-1 IAO with 2 Inverted Inputs

$$ZN = (!(((!A1) \& (!A2)) | B))$$



## Function Table

A1	A2	B	ZN
0	0	X	0
0	1	0	1
0	1	1	0
1	X	0	1
1	X	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_IAO21HSV1	1.26	0.98
LVT_IAO21HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00079	0.00084
A2	0.00086	0.00091
B	0.00036	0.00039

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00053	0.00053
A2	0.00057	0.00057
B	0.00063	0.00068

## Max Leakage Power (uW)

V1	V2
0.00332033	0.00314674

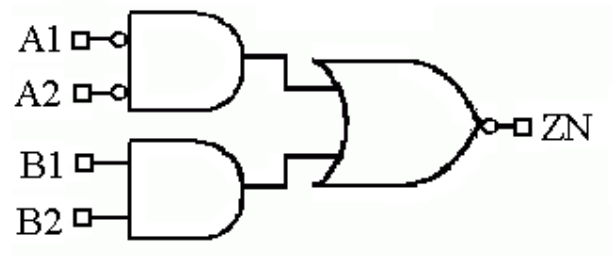
## Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.03576	0.03506
A1→ZN_RISE	0.02947	0.03092
A2→ZN_FALL	0.03805	0.03735
A2→ZN_RISE	0.03094	0.03238
B→ZN_FALL	0.01016	0.00870
B→ZN_RISE	0.01782	0.01878

# LVT\_IAO22HS

## Cell Description

2-2 IAO with 2 Inverted Inputs  
 $ZN = (!(((!A1) \& (!A2)) | (B1 \& B2)))$



## Function Table

B1	B2	A1	A2	ZN
0	X	0	0	0
0	X	0	1	1
0	X	1	X	1
1	0	0	0	0
1	0	0	1	1
1	0	1	X	1
1	1	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_IAO22HSV1	1.26	1.26
LVT_IAO22HSV2	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00086	0.00089
A2	0.00092	0.00095
B1	0.00052	0.00052
B2	0.00059	0.00060

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00051	0.00051
A2	0.00057	0.00057
B1	0.00073	0.00071
B2	0.00073	0.00074

## Max Leakage Power (uW)

V1	V2
0.00302922	0.00316448

### Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.03846	0.03696
A1→ZN_RISE	0.03123	0.03205
A2→ZN_FALL	0.03998	0.03851
A2→ZN_RISE	0.03237	0.03323
B1→ZN_FALL	0.01462	0.01461
B1→ZN_RISE	0.02263	0.02279
B2→ZN_FALL	0.01574	0.01581
B2→ZN_RISE	0.02534	0.02559



# LVT\_INAND2HS

## Cell Description

2-Input NAND with 1 Inverted Input

$$ZN = \neg((\neg A1) \& B1)$$



## Function Table

A1	B1	ZN
0	0	1
0	1	0
1	X	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_INAND2HSV1	1.26	0.84
LVT_INAND2HSV2	1.26	0.84

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00072	0.00077
B1	0.00034	0.00036

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00050	0.00052
B1	0.00063	0.00067

## Max Leakage Power (uW)

V1	V2
0.00292209	0.00344456

## Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.02808	0.02946
A1→ZN_RISE	0.02461	0.02324

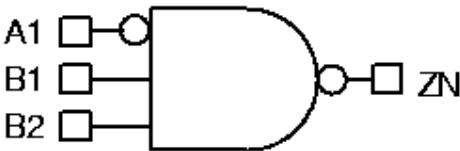
B1→ZN_FALL	0.01201	0.01270
B1→ZN_RISE	0.01334	0.01137

# LVT\_INAND3HS

## Cell Description

3-Input NAND with 1 Inverted Input

$$Z_N = \neg((\neg A_1) \& B_1 \& B_2)$$



## Function Table

A1	B1	B2	ZN
0	0	X	1
0	1	0	1
0	1	1	0
1	X	X	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_INAND3HSV1	1.26	0.98
LVT_INAND3HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00082	0.00090
B1	0.00042	0.00046
B2	0.00050	0.00054

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00052	0.00053
B1	0.00062	0.00067
B2	0.00065	0.00071

## Max Leakage Power (uW)

V1	V2
0.00453464	0.00519725

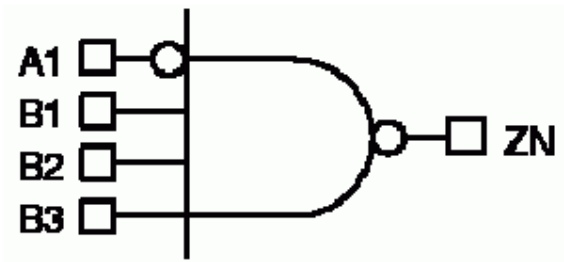
## Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.03396	0.03641
A1→ZN_RISE	0.02677	0.02533
B1→ZN_FALL	0.01803	0.01943
B1→ZN_RISE	0.01481	0.01230
B2→ZN_FALL	0.01961	0.02092
B2→ZN_RISE	0.01652	0.01352

# LVT\_INAND4HS

## Cell Description

4-Input NAND with 1 Inverted Input  
 $ZN = \neg((\neg A1) \& B1 \& B2 \& B3)$



## Function Table

A1	B1	B2	B3	ZN
0	0	X	X	1
0	1	0	X	1
0	1	1	0	1
0	1	1	1	0
1	X	X	X	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_INAND4HSV1	1.26	1.12
LVT_INAND4HSV2	1.26	1.12

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00090	0.00096
B1	0.00045	0.00049
B2	0.00053	0.00058
B3	0.00061	0.00065

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00053	0.00053
B1	0.00065	0.00069
B2	0.00062	0.00067
B3	0.00062	0.00067

## Max Leakage Power (uW)

V1	V2
0.00606738	0.00742756

**Delay Table (ns)**

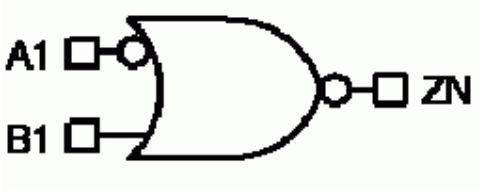
Description	V1	V2
A1→ZN_FALL	0.03986	0.04229
A1→ZN_RISE	0.02876	0.02742
B1→ZN_FALL	0.02305	0.02481
B1→ZN_RISE	0.01526	0.01315
B2→ZN_FALL	0.02615	0.02789
B2→ZN_RISE	0.01699	0.01444
B3→ZN_FALL	0.02741	0.02914
B3→ZN_RISE	0.01838	0.01547

# LVT\_INOR2HS

## Cell Description

2-Input NOR with 1 Inverted Input

$$ZN = \neg((\neg A1) \vee B1)$$



## Function Table

A1	B1	ZN
0	X	0
1	0	1
1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_INOR2HSV1	1.26	0.84
LVT_INOR2HSV2	1.26	0.84

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00073	0.00077
B1	0.00033	0.00039

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00051	0.00051
B1	0.00061	0.00067

## Max Leakage Power (uW)

V1	V2
0.00292510	0.00286834

## Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.02562	0.02669
A1→ZN_RISE	0.03281	0.02902

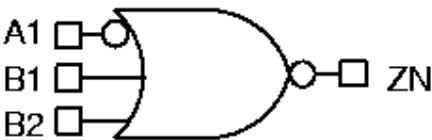
B1→ZN_FALL	0.00838	0.00895
B1→ZN_RISE	0.02254	0.01894



# LVT\_INOR3HS

## Cell Description

3-Input NOR with 1 Inverted Input  
 $ZN = \neg((\neg A1) \vee B1 \vee B2)$



## Function Table

A1	B1	B2	ZN
0	X	X	0
1	0	0	1
1	0	1	0
1	1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_INOR3HSV1	1.26	0.98
LVT_INOR3HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00083	0.00091
B1	0.00043	0.00048
B2	0.00053	0.00058

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00052	0.00052
B1	0.00064	0.00069
B2	0.00064	0.00069

## Max Leakage Power (uW)

V1	V2
0.00399058	0.00372220

## Delay Table (ns)

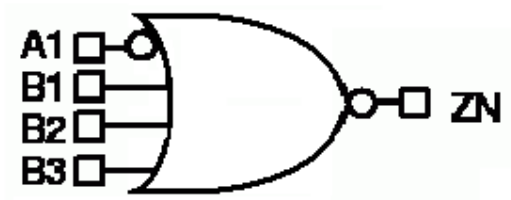
Description	V1	V2
A1→ZN_FALL	0.02985	0.02920
A1→ZN_RISE	0.03707	0.04004
B1→ZN_FALL	0.01106	0.00955
B1→ZN_RISE	0.02846	0.03088
B2→ZN_FALL	0.01173	0.00991
B2→ZN_RISE	0.03066	0.03302

# LVT\_INOR4HS

## Cell Description

4-Input NOR with 1 Inverted Input

$$ZN = \neg((\neg A1) \vee B1 \vee B2 \vee B3)$$



## Function Table

A1	B1	B2	B3	ZN
0	X	X	X	0
1	0	0	0	1
1	0	0	1	0
1	0	1	X	0
1	1	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_INOR4HSV1	1.26	1.12
LVT_INOR4HSV2	1.26	1.12

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00089	0.00096
B1	0.00046	0.00051
B2	0.00056	0.00061
B3	0.00066	0.00071

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00052	0.00052
B1	0.00061	0.00066
B2	0.00064	0.00069
B3	0.00064	0.00069

## Max Leakage Power (uW)

V1	V2
0.00500010	0.00459946

**Delay Table (ns)**

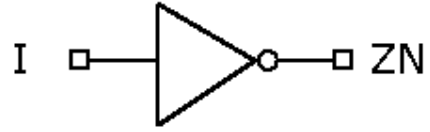
Description	V1	V2
A1→ZN_FALL	0.03129	0.03052
A1→ZN_RISE	0.04560	0.04969
B1→ZN_FALL	0.01152	0.00993
B1→ZN_RISE	0.03800	0.04157
B2→ZN_FALL	0.01222	0.01031
B2→ZN_RISE	0.04264	0.04648
B3→ZN_FALL	0.01227	0.01028
B3→ZN_RISE	0.04457	0.04847

# LVT\_INHS

## Cell Description

Inverter

$ZN = (!I)$



## Function Table

I	ZN
0	1
1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_INHSV1	1.26	0.42
LVT_INHSV2	1.26	0.42
LVT_INHSV3	1.26	0.56
LVT_INHSV4	1.26	0.56
LVT_INHSV6	1.26	0.84
LVT_INHSV8	1.26	0.98
LVT_INHSV12	1.26	1.26
LVT_INHSV16	1.26	1.68
LVT_INHSV20	1.26	2.10
LVT_INHSV24	1.26	2.38

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
I	0.00020	0.00025	0.00032	0.00037	0.00060	0.00070	0.00095	0.00135

Pin	V20	V24
I	0.00170	0.00199

## Pin Capacitance (pf)

Pin	V1	V2	V3	V4	V6	V8	V12	V16
I	0.00059	0.00071	0.00110	0.00130	0.00185	0.00244	0.00329	0.00478

Pin	V20	V24
I	0.00591	0.00704

### Max Leakage Power (uW)

V1	V2	V3	V4	V6	V8	V12	V16
0.00098749	0.00110719	0.00217302	0.00257747	0.00509461	0.00764924	0.01258147	0.01898741

V20	V24
0.02544029	0.03141931

### Delay Table (ns)

Description	V1	V2	V3	V4	V6	V8	V12	V16
I→ZN_FALL	0.00853	0.00775	0.00656	0.00611	0.00583	0.00536	0.00588	0.00536
I→ZN_RISE	0.01148	0.01009	0.00833	0.00782	0.00746	0.00679	0.00625	0.00658

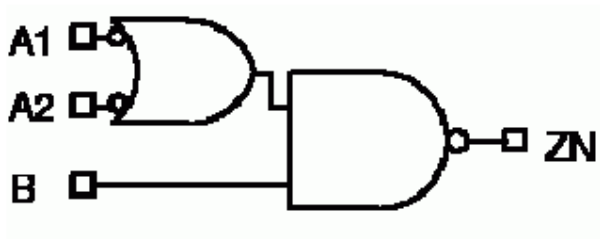
Description	V20	V24
I→ZN_FALL	0.00563	0.00588
I→ZN_RISE	0.00683	0.00701

# LVT\_IOA21HS

## Cell Description

2-1 IOA with 2 Inverted Inputs

$$ZN=((!(A1)|(A2))\&B)$$



## Function Table

A1	A2	B	ZN
0	X	0	1
0	X	1	0
1	0	0	1
1	0	1	0
1	1	X	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_IOA21HSV1	1.26	0.98
LVT_IOA21HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00078	0.00085
A2	0.00086	0.00093
B	0.00034	0.00038

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00058	0.00058
A2	0.00059	0.00059
B	0.00061	0.00067

## Max Leakage Power (uW)

V1	V2
0.00347796	0.00410970

## Delay Table (ns)

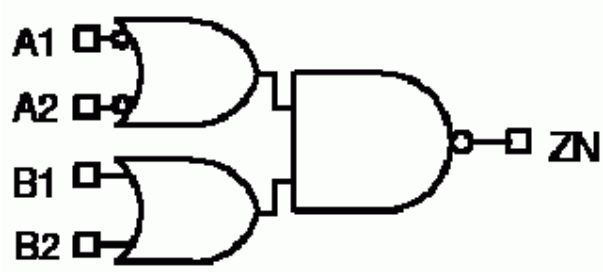
Description	V1	V2
A1→ZN_FALL	0.03045	0.03238
A1→ZN_RISE	0.02600	0.02464
A2→ZN_FALL	0.03301	0.03495
A2→ZN_RISE	0.02761	0.02621
B→ZN_FALL	0.01194	0.01282
B→ZN_RISE	0.01335	0.01121



# LVT\_IOA22HS

## Cell Description

2-2 IOA with 2 Inverted Inputs  
 $ZN = (!(((!A1) | (!A2)) \& (B1 | B2)))$



## Function Table

B1	B2	A1	A2	ZN
0	0	X	X	1
0	1	0	X	0
0	1	1	0	0
0	1	1	1	1
1	X	0	X	0
1	X	1	0	0
1	X	1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_IOA22HSV1	1.26	1.26
LVT_IOA22HSV2	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00085	0.00088
A2	0.00092	0.00095
B1	0.00047	0.00045
B2	0.00056	0.00055

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00059	0.00059
A2	0.00060	0.00059
B1	0.00063	0.00063
B2	0.00072	0.00073

## Max Leakage Power (uW)

V1	V2
0.00351071	0.00411521

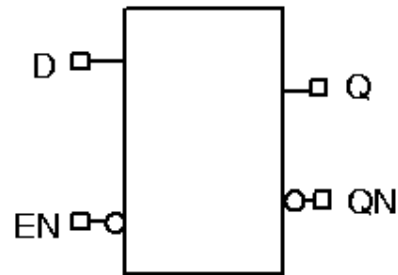
### **Delay Table (ns)**

Description	V1	V2
A1→ZN_FALL	0.03243	0.03359
A1→ZN_RISE	0.02751	0.02571
A2→ZN_FALL	0.03514	0.03616
A2→ZN_RISE	0.02889	0.02699
B1→ZN_FALL	0.01502	0.01472
B1→ZN_RISE	0.02285	0.02206
B2→ZN_FALL	0.01685	0.01655
B2→ZN_RISE	0.02524	0.02441

# LVT\_LALHS

## Cell Description

Low Enable Latch  
Q = !EN ? D : pre\_Q  
QN = !Q



## Function Table

EN	D	Q
0	0	0
0	1	1
1	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_LALHSV1	1.26	2.24
LVT_LALHSV2	1.26	2.24

## Pin Power (uW/MHz)

Pin	V1	V2
D	0.00002	0.00002
EN	0.00113	0.00113
Q	0.00095	0.00108
QN	0.00096	0.00107

## Pin Capacitance (pf)

Pin	V1	V2
D	0.00070	0.00070
EN	0.00052	0.00052

## Max Leakage Power (uW)

V1	V2
0.00508670	0.00521508

## Delay Table (ns)

Description	V1	V2
-------------	----	----

D→Q_FALL	0.04477	0.04564
D→Q_RISE	0.03900	0.03849
EN→Q_FALL	0.07518	0.07595
EN→Q_RISE	0.06715	0.06658
D→QN_FALL	0.05399	0.05665
D→QN_RISE	0.06346	0.06564
EN→QN_FALL	0.08242	0.08507
EN→QN_RISE	0.09390	0.09599

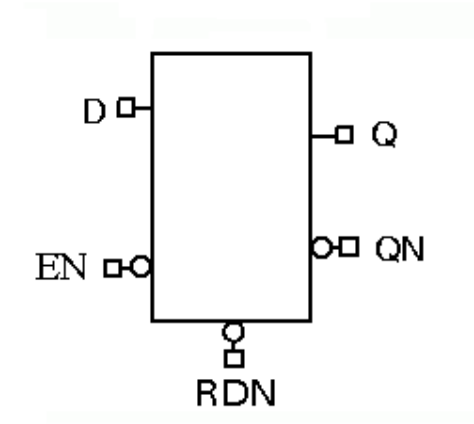
### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→EN	-0.01145	-0.01432
D	hold_RISE→EN	-0.01718	-0.01719
D	setup_FALL→EN	0.02577	0.03148
D	setup_RISE→EN	0.02291	0.02577
EN	minpwl	0.05868	0.06186

# LVT\_LALRNHS

## Cell Description

Latch  
Q = !RDN ? 0 : !EN ? D : pre\_Q  
QN = !Q



## Function Table

RDN	EN	D	Q
0	X	X	0
1	0	0	0
1	0	1	1
1	1	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_LALRNHSV1	1.26	2.66
LVT_LALRNHSV2	1.26	2.66

## Pin Power (uW/MHz)

Pin	V1	V2
D	0.00002	0.00002
EN	0.00120	0.00120
Q	0.00112	0.00126
QN	0.00112	0.00125
RDN	0.00001	0.00001

## Pin Capacitance (pf)

Pin	V1	V2
D	0.00065	0.00065
EN	0.00052	0.00053
RDN	0.00093	0.00094

## Max Leakage Power (uW)

V1	V2
0.00576399	0.00602230

### Delay Table (ns)

Description	V1	V2
D→Q_FALL	0.05020	0.05090
D→Q_RISE	0.05373	0.05333
EN→Q_FALL	0.08124	0.08188
EN→Q_RISE	0.07985	0.07950
RDN→Q_FALL	0.04959	0.05017
RDN→Q_RISE	0.05681	0.05643
D→QN_FALL	0.07235	0.07570
D→QN_RISE	0.06833	0.07074
EN→QN_FALL	0.09871	0.10214
EN→QN_RISE	0.09939	0.10178
RDN→QN_RISE	0.06828	0.07064
RDN→QN_FALL	0.07542	0.07878

### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→EN	-0.01433	-0.01718
D	hold_RISE→EN	-0.03150	-0.03149
D	setup_FALL→EN	0.03150	0.03721
D	setup_RISE→EN	0.03721	0.04294
RDN	setup_RISE→EN	0.04009	0.04580
RDN	hold_RISE→EN	-0.03435	-0.03436
EN	minpwl	0.07134	0.07453
RDN	minpwl	0.06819	0.07139

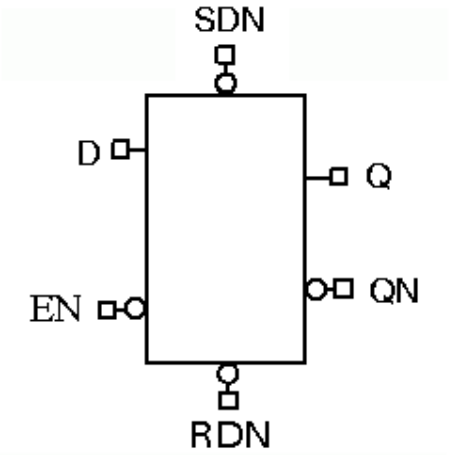
# LVT\_LALRSNHS

## Cell Description

Low Enable Latch with Clear and Set

$Q = !SDN ? 1 : !RDN ? 0 : !EN ? D : pre\_Q$

$QN = !Q$



## Function Table

RDN	SDN	EN	D	Q
0	0	X	X	1
0	1	X	X	0
1	0	X	X	1
1	1	0	0	0
1	1	0	1	1
1	1	1	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_LALRSNHSV1	1.26	3.92
LVT_LALRSNHSV2	1.26	4.06

## Pin Power (uW/MHz)

Pin	V1	V2
D	0.00002	0.00002
EN	0.00133	0.00137
Q	0.00135	0.00148
QN	0.00132	0.00141
RDN	0.00002	0.00002
SDN	0.00059	0.00059

## Pin Capacitance (pf)

Pin	V1	V2
D	0.00065	0.00066
EN	0.00051	0.00051
RDN	0.00098	0.00099
SDN	0.00050	0.00051

### Max Leakage Power (uW)

V1	V2
0.00524800	0.00661071

### Delay Table (ns)

Description	V1	V2
D→Q_FALL	0.07925	0.07795
D→Q_RISE	0.06060	0.05795
EN→Q_FALL	0.10961	0.10951
EN→Q_RISE	0.08426	0.08300
RDN→Q_FALL	0.09422	0.09280
RDN→Q_RISE	0.06438	0.06216
SDN→Q_FALL	0.10470	0.10243
SDN→Q_RISE	0.07094	0.06866
D→QN_FALL	0.07970	0.07900
D→QN_RISE	0.09721	0.09770
EN→QN_FALL	0.10366	0.10416
EN→QN_RISE	0.12774	0.12946
RDN→QN_RISE	0.11334	0.11443
RDN→QN_FALL	0.08349	0.08316
SDN→QN_FALL	0.08847	0.08767
SDN→QN_RISE	0.12304	0.12282

### Timing Constraints (ns)

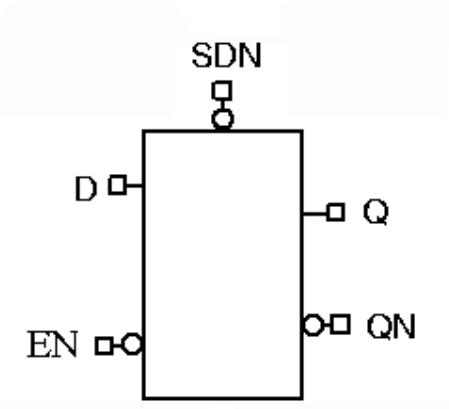
Pin	Requirement	V1	V2
D	hold_FALL→EN	-0.03435	-0.04006
D	hold_RISE→EN	-0.03435	-0.03722
D	setup_FALL→EN	0.05725	0.06582
D	setup_RISE→EN	0.04581	0.05153
RDN	setup_RISE→EN	0.04868	0.05727
RDN	hold_RISE→EN	-0.04009	-0.04008
SDN	setup_RISE→EN	0.07728	0.08587
SDN	hold_RISE→EN	-0.06011	-0.06297
SDN	non_seq_hold_RISE→RDN	-0.09732	-0.10304
SDN	non_seq_setup_RISE→RDN	0.12022	0.12881
EN	minpwl	0.07137	0.08090
RDN	minpwl	0.10947	0.11899
SDN	minpwl	0.05864	0.06184



# LVT\_LALSNHS

## Cell Description

Latch  
Q = !SDN ? 1 : !EN ? D : pre\_Q  
QN = !Q



## Function Table

SDN	EN	D	Q
0	X	X	1
1	0	0	0
1	0	1	1
1	1	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_LALSNHSV1	1.26	2.94
LVT_LALSNHSV2	1.26	2.94

## Pin Power (uW/MHz)

Pin	V1	V2
D	0.00001	0.00001
EN	0.00121	0.00121
Q	0.00116	0.00129
QN	0.00114	0.00125
SDN	0.00052	0.00051

## Pin Capacitance (pf)

Pin	V1	V2
D	0.00063	0.00063
EN	0.00052	0.00052
SDN	0.00067	0.00069

## Max Leakage Power (uW)

V1	V2
0.00577785	0.00631538

### Delay Table (ns)

Description	V1	V2
D→Q_FALL	0.06747	0.06796
D→Q_RISE	0.04332	0.04242
EN→Q_FALL	0.09553	0.09579
EN→Q_RISE	0.07293	0.07221
SDN→Q_FALL	0.08832	0.08868
SDN→Q_RISE	0.06518	0.06403
D→QN_FALL	0.05986	0.06183
D→QN_RISE	0.08713	0.08956
EN→QN_FALL	0.08972	0.09188
EN→QN_RISE	0.11522	0.11747
SDN→QN_FALL	0.08163	0.08324
SDN→QN_RISE	0.10797	0.11030

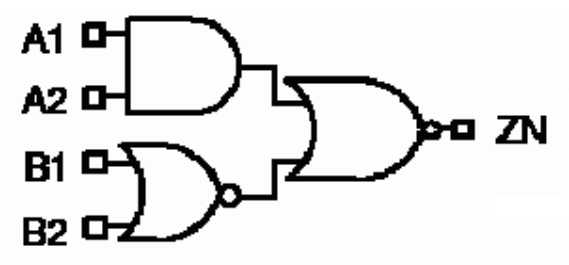
### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→EN	-0.03435	-0.03722
D	hold_RISE→EN	-0.02004	-0.02004
D	setup_FALL→EN	0.05726	0.06298
D	setup_RISE→EN	0.02576	0.02864
SDN	setup_RISE→EN	0.07730	0.08302
SDN	hold_RISE→EN	-0.05724	-0.06012
EN	minpwl	0.06186	0.06505
SDN	minpwl	0.05231	0.05547

# LVT\_MAOI22HS

## Cell Description

the logical NOR of one AND2 and one NOR2 block.  
 $ZN = \neg((A1 \& A2) | (\neg(B1 \& B2)))$



## Function Table

A1	A2	B1	B2	ZN
0	X	0	0	0
0	X	0	1	1
0	X	1	X	1
1	0	0	0	0
1	0	0	1	1
1	0	1	X	1
1	1	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_MAOI22HSV1	1.26	1.26
LVT_MAOI22HSV2	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00060	0.00061
A2	0.00052	0.00053
B1	0.00086	0.00089
B2	0.00092	0.00095

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00075	0.00075
A2	0.00072	0.00072
B1	0.00054	0.00054
B2	0.00057	0.00057

## Max Leakage Power (uW)

V1	V2
0.00300871	0.00317117

### **Delay Table (ns)**

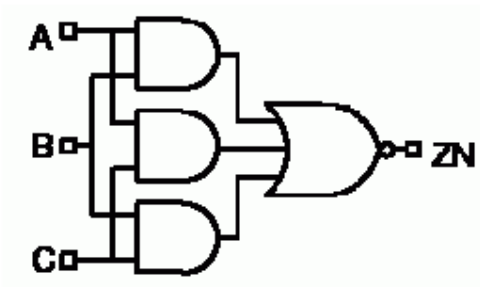
Description	V1	V2
A1→ZN_FALL	0.01587	0.01593
A1→ZN_RISE	0.02548	0.02573
A2→ZN_FALL	0.01465	0.01470
A2→ZN_RISE	0.02272	0.02296
B1→ZN_FALL	0.03873	0.03706
B1→ZN_RISE	0.03135	0.03211
B2→ZN_FALL	0.03994	0.03846
B2→ZN_RISE	0.03235	0.03321

# LVT\_MAOI222HS

## Cell Description

Inverting 2 of 3 MAJORITY

$$ZN = \neg((A \& B) | (B \& C) | (A \& C))$$



## Function Table

A	B	C	ZN
0	0	X	1
0	1	0	1
0	1	1	0
1	0	0	1
1	0	1	0
1	1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_MAOI222HSV1	1.26	1.54
LVT_MAOI222HSV2	1.26	1.54

## Pin Power (uW/MHz)

Pin	V1	V2
A	0.00069	0.00089
B	0.00060	0.00077
C	0.00078	0.00100

## Pin Capacitance (pf)

Pin	V1	V2
A	0.00121	0.00144
B	0.00107	0.00131
C	0.00110	0.00134

## Max Leakage Power (uW)

V1	V2
0.00202534	0.00255523

**Delay Table (ns)**

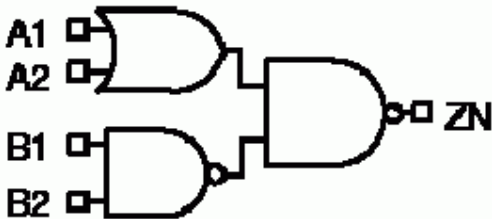
Description	V1	V2
A→ZN_FALL	0.02114	0.01938
A→ZN_RISE	0.04532	0.04116
B→ZN_FALL	0.02067	0.01914
B→ZN_RISE	0.04243	0.03880
C→ZN_FALL	0.02224	0.02048
C→ZN_RISE	0.04781	0.04369

# LVT\_MOAI22HS

## Cell Description

the logical NAND of one OR2 and one NAND2 block.

$$ZN = \neg((A1 \vee A2) \wedge \neg(B1 \wedge B2))$$



## Function Table

A1	A2	B1	B2	ZN
0	0	X	X	1
0	1	0	X	0
0	1	1	0	0
0	1	1	1	1
1	X	0	X	0
1	X	1	0	0
1	X	1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_MOAI22HSV1	1.26	1.26
LVT_MOAI22HSV2	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00047	0.00047
A2	0.00056	0.00057
B1	0.00086	0.00089
B2	0.00092	0.00095

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00063	0.00063
A2	0.00073	0.00073
B1	0.00075	0.00075
B2	0.00059	0.00058

## Max Leakage Power (uW)

V1	V2
0.00346092	0.00407492

### Delay Table (ns)

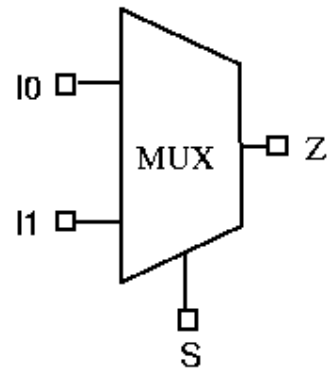
Description	V1	V2
A1→ZN_FALL	0.01497	0.01516
A1→ZN_RISE	0.02275	0.02276
A2→ZN_FALL	0.01693	0.01710
A2→ZN_RISE	0.02521	0.02521
B1→ZN_FALL	0.03289	0.03385
B1→ZN_RISE	0.02797	0.02602
B2→ZN_FALL	0.03524	0.03609
B2→ZN_RISE	0.02900	0.02700



# LVT\_MUX2HS

## Cell Description

2-to-1 Multiplexer  
 $Z=((I0\&(!S))|(I1\&S))$



## Function Table

S	I0	I1	Z
0	0	X	0
0	1	X	1
1	X	0	0
1	X	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_MUX2HSV1	1.26	1.68
LVT_MUX2HSV2	1.26	1.68

## Pin Power (uW/MHz)

Pin	V1	V2
I0	0.00109	0.00117
I1	0.00093	0.00100
S	0.00115	0.00123

## Pin Capacitance (pf)

Pin	V1	V2
I0	0.00060	0.00060
I1	0.00063	0.00063
S	0.00099	0.00099

## Max Leakage Power (uW)

V1	V2
0.00728267	0.00749461

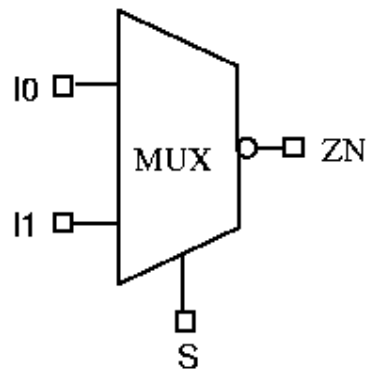
## Delay Table (ns)

Description	V1	V2
I0→Z_FALL	0.03938	0.03976
I0→Z_RISE	0.03556	0.03522
I1→Z_FALL	0.03435	0.03458
I1→Z_RISE	0.03019	0.02970
S→Z_FALL	0.03127	0.03167
S→Z_RISE	0.03211	0.03173

# LVT\_MUX2NHS

## Cell Description

2-to-1 Inverting Multiplexer  
 $ZN = \neg((I0 \& \neg S) | (I1 \& S))$



## Function Table

S	I0	I1	ZN
0	0	X	1
0	1	X	0
1	X	0	1
1	X	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_MUX2NHVS1	1.26	1.54
LVT_MUX2NHVS2	1.26	1.68

## Pin Power (uW/MHz)

Pin	V1	V2
I0	0.00063	0.00070
I1	0.00067	0.00075
S	0.00068	0.00077

## Pin Capacitance (pf)

Pin	V1	V2
I0	0.00060	0.00059
I1	0.00061	0.00061
S	0.00102	0.00108

## Max Leakage Power (uW)

V1	V2
0.00477412	0.00489836

## Delay Table (ns)

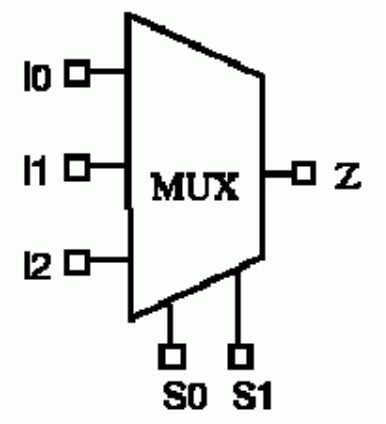
Description	V1	V2
I0→ZN_FALL	0.01971	0.02048
I0→ZN_RISE	0.02417	0.02530
I1→ZN_FALL	0.01931	0.02009
I1→ZN_RISE	0.02633	0.02796
S→ZN_FALL	0.01689	0.01708
S→ZN_RISE	0.01724	0.01799

# LVT\_MUX3HS

## Cell Description

3-to-1 Multiplexer

$$Z=((I0\&(!S0)\&(!S1))|(I1\&S0\&(!S1))|(I2\&S1))$$



## Function Table

S1	S0	I0	I1	I2	Z
0	0	0	X	X	0
0	0	1	X	X	1
0	1	X	0	X	0
0	1	X	1	X	1
1	X	X	X	0	0
1	X	X	X	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_MUX3HSV1	1.26	3.50
LVT_MUX3HSV2	1.26	3.50

## Pin Power (uW/MHz)

Pin	V1	V2
I0	0.00257	0.00268
I1	0.00228	0.00239
I2	0.00202	0.00214
S0	0.00292	0.00303
S1	0.00201	0.00211

## Pin Capacitance (pf)

Pin	V1	V2
I0	0.00069	0.00069
I1	0.00065	0.00065
I2	0.00075	0.00076
S0	0.00157	0.00157
S1	0.00120	0.00120

### Max Leakage Power (uW)

V1	V2
0.00985828	0.00955149

### Delay Table (ns)

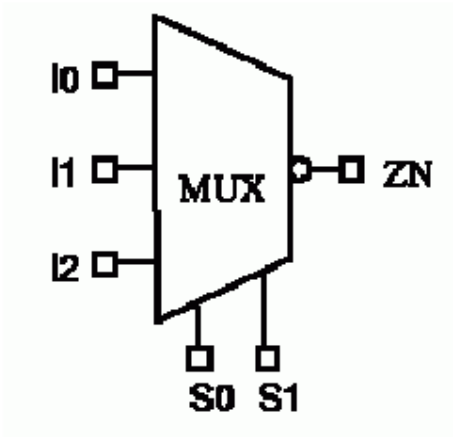
Description	V1	V2
I0→Z_FALL	0.07712	0.07799
I0→Z_RISE	0.07536	0.07583
I1→Z_FALL	0.06878	0.06971
I1→Z_RISE	0.06878	0.06938
I2→Z_FALL	0.05245	0.05371
I2→Z_RISE	0.05718	0.05811
S0→Z_FALL	0.08045	0.08140
S0→Z_RISE	0.07768	0.07824
S1→Z_FALL	0.04710	0.04780
S1→Z_RISE	0.05389	0.05441

# LVT\_MUX3NHS

## Cell Description

3-to-1 Inverting Multiplexer

$$ZN = \neg((I0 \& \neg S0 \& \neg S1) \vee (I1 \& S0 \& \neg S1) \vee (I2 \& S1))$$



## Function Table

S1	S0	I0	I1	I2	ZN
0	0	0	X	X	1
0	0	1	X	X	0
0	1	X	0	X	1
0	1	X	1	X	0
1	X	X	X	0	1
1	X	X	X	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_MUX3NHSV1	1.26	3.08
LVT_MUX3NHSV2	1.26	3.08

## Pin Power (uW/MHz)

Pin	V1	V2
I0	0.00204	0.00212
I1	0.00175	0.00184
I2	0.00149	0.00157
S0	0.00239	0.00255
S1	0.00147	0.00155

## Pin Capacitance (pf)

Pin	V1	V2
I0	0.00069	0.00070
I1	0.00066	0.00066
I2	0.00076	0.00076
S0	0.00157	0.00139
S1	0.00119	0.00119

### Max Leakage Power (uW)

V1	V2
0.00907689	0.01050280

### Delay Table (ns)

Description	V1	V2
I0→ZN_FALL	0.06181	0.06072
I0→ZN_RISE	0.06683	0.06518
I1→ZN_FALL	0.05528	0.05448
I1→ZN_RISE	0.05851	0.05728
I2→ZN_FALL	0.04368	0.04322
I2→ZN_RISE	0.04282	0.04148
S0→ZN_FALL	0.06429	0.06434
S0→ZN_RISE	0.07015	0.06951
S1→ZN_FALL	0.03985	0.03944
S1→ZN_RISE	0.03693	0.03555

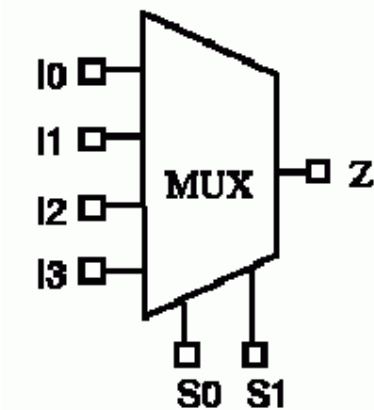


# LVT\_MUX4HS

## Cell Description

4-to-1 Multiplexer

$$Z=((I0\&(!S0)\&(!S1))|(I1\&S0\&(!S1))|(I2\&(!S0)\&S1)|(I3\&S0\&S1))$$



## Function Table

S1	S0	I0	I1	I2	I3	Z
0	0	0	X	X	X	0
0	0	1	X	X	X	1
0	1	X	0	X	X	0
0	1	X	1	X	X	1
1	0	X	X	0	X	0
1	0	X	X	1	X	1
1	1	X	X	X	0	0
1	1	X	X	X	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_MUX4HSV1	1.26	4.06
LVT_MUX4HSV2	1.26	4.06

## Pin Power (uW/MHz)

Pin	V1	V2
I0	0.00210	0.00220
I1	0.00244	0.00254
I2	0.00235	0.00244
I3	0.00260	0.00270
S0	0.00195	0.00205
S1	0.00350	0.00360

## Pin Capacitance (pf)

Pin	V1	V2
I0	0.00070	0.00070
I1	0.00084	0.00083
I2	0.00067	0.00067
I3	0.00067	0.00067

S0	0.00153	0.00153
S1	0.00222	0.00221

### Max Leakage Power (uW)

V1	V2
0.01083365	0.01058576

### Delay Table (ns)

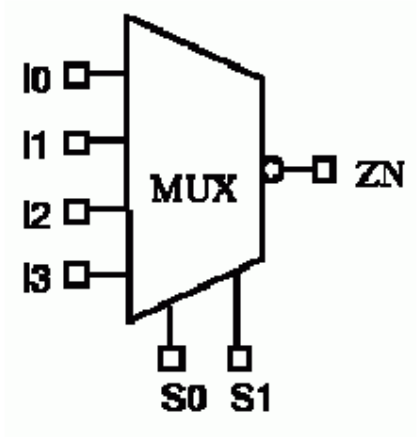
Description	V1	V2
I0→Z_FALL	0.06446	0.06502
I0→Z_RISE	0.06249	0.06226
I1→Z_FALL	0.07431	0.07515
I1→Z_RISE	0.07694	0.07689
I2→Z_FALL	0.07152	0.07202
I2→Z_RISE	0.06742	0.06714
I3→Z_FALL	0.07627	0.07709
I3→Z_RISE	0.07987	0.07980
S0→Z_FALL	0.04595	0.04678
S0→Z_RISE	0.05567	0.05575
S1→Z_FALL	0.08019	0.08086
S1→Z_RISE	0.07910	0.07893

# LVT\_MUX4NHS

## Cell Description

4-to-1 Inverting Multiplexer

$$ZN = \neg((I0 \& \neg S0 \& \neg S1) \vee (I1 \& S0 \& \neg S1) \vee (I2 \& \neg S0 \& S1) \vee (I3 \& S0 \& S1))$$



## Function Table

S1	S0	I0	I1	I2	I3	ZN
0	0	0	X	X	X	1
0	0	1	X	X	X	0
0	1	X	0	X	X	1
0	1	X	1	X	X	0
1	0	X	X	0	X	1
1	0	X	X	1	X	0
1	1	X	X	X	0	1
1	1	X	X	X	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_MUX4NHSV1	1.26	3.78
LVT_MUX4NHSV2	1.26	3.78

## Pin Power (uW/MHz)

Pin	V1	V2
I0	0.00154	0.00165
I1	0.00189	0.00200
I2	0.00179	0.00189
I3	0.00205	0.00216
S0	0.00140	0.00150
S1	0.00295	0.00305

## Pin Capacitance (pf)

Pin	V1	V2
I0	0.00070	0.00070
I1	0.00083	0.00084
I2	0.00067	0.00067
I3	0.00067	0.00067

S0	0.00153	0.00153
S1	0.00221	0.00221

### Max Leakage Power (uW)

V1	V2
0.01032741	0.01023227

### Delay Table (ns)

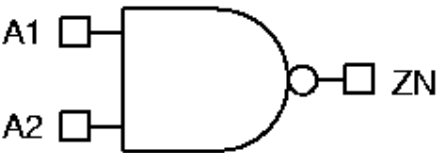
Description	V1	V2
I0→ZN_FALL	0.04824	0.04833
I0→ZN_RISE	0.05353	0.05329
I1→ZN_FALL	0.06138	0.06237
I1→ZN_RISE	0.06343	0.06297
I2→ZN_FALL	0.05233	0.05320
I2→ZN_RISE	0.06057	0.06029
I3→ZN_FALL	0.06420	0.06531
I3→ZN_RISE	0.06533	0.06499
S0→ZN_FALL	0.04000	0.04104
S0→ZN_RISE	0.03537	0.03484
S1→ZN_FALL	0.06406	0.06479
S1→ZN_RISE	0.06918	0.06892

# LVT\_NAND2HS

## Cell Description

2-Input NAND

$$Z_N = \neg(A_1 \& A_2)$$



## Function Table

A1	A2	ZN
0	X	1
1	0	1
1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_NAND2HSV1	1.26	0.70
LVT_NAND2HSV2	1.26	0.70
LVT_NAND2HSV3	1.26	0.98
LVT_NAND2HSV8	1.26	1.68

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V8
A1	0.00027	0.00030	0.00046	0.00097
A2	0.00035	0.00038	0.00061	0.00148

## Pin Capacitance (pf)

Pin	V1	V2	V3	V8
A1	0.00060	0.00067	0.00103	0.00231
A2	0.00063	0.00069	0.00123	0.00244

## Max Leakage Power (uW)

V1	V2	V3	V8
0.00203403	0.00284202	0.00592124	0.01901995

## Delay Table (ns)

Description	V1	V2	V3	V8
-------------	----	----	----	----

A1→ZN_FALL	0.01079	0.01144	0.01020	0.00855
A1→ZN_RISE	0.01248	0.01046	0.00921	0.00776
A2→ZN_FALL	0.01209	0.01275	0.01203	0.01086
A2→ZN_RISE	0.01413	0.01156	0.01096	0.00942

# LVT\_NAND3HS

## Cell Description

3-Input NAND

$$Z_N = \neg(A_1 \& A_2 \& A_3)$$



## Function Table

A1	A2	A3	ZN
0	X	X	1
1	0	X	1
1	1	0	1
1	1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_NAND3HSV1	1.26	0.84
LVT_NAND3HSV2	1.26	0.84
LVT_NAND3HSV3	1.26	1.26
LVT_NAND3HSV8	1.26	2.52

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V8
A1	0.00035	0.00040	0.00056	0.00128
A2	0.00044	0.00049	0.00071	0.00175
A3	0.00051	0.00056	0.00081	0.00210

## Pin Capacitance (pf)

Pin	V1	V2	V3	V8
A1	0.00058	0.00065	0.00097	0.00228
A2	0.00062	0.00070	0.00118	0.00244
A3	0.00063	0.00070	0.00122	0.00242

## Max Leakage Power (uW)

V1	V2	V3	V8
0.00344315	0.00489435	0.00668535	0.02563339

**Delay Table (ns)**

Description	V1	V2	V3	V8
A1→ZN_FALL	0.01566	0.01718	0.01442	0.01262
A1→ZN_RISE	0.01399	0.01183	0.01039	0.00879
A2→ZN_FALL	0.01803	0.01967	0.01756	0.01649
A2→ZN_RISE	0.01539	0.01274	0.01207	0.01036
A3→ZN_FALL	0.01920	0.02078	0.01861	0.01801
A3→ZN_RISE	0.01706	0.01386	0.01334	0.01141

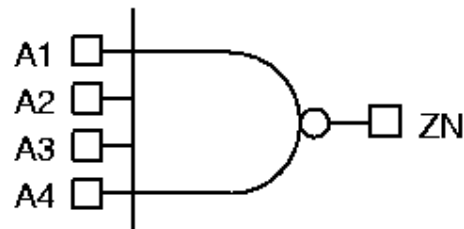


# LVT\_NAND4HS

## Cell Description

4-Input NAND

$ZN = \neg(A1 \& A2 \& A3 \& A4)$



## Function Table

A1	A2	A3	A4	ZN
0	X	X	X	1
1	0	X	X	1
1	1	0	X	1
1	1	1	0	1
1	1	1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_NAND4HSV1	1.26	0.98
LVT_NAND4HSV2	1.26	0.98
LVT_NAND4HSV3	1.26	1.68
LVT_NAND4HSV8	1.26	2.24

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V8
A1	0.00033	0.00045	0.00063	0.00312
A2	0.00041	0.00053	0.00078	0.00320
A3	0.00049	0.00062	0.00093	0.00328
A4	0.00057	0.00069	0.00102	0.00336

## Pin Capacitance (pf)

Pin	V1	V2	V3	V8
A1	0.00054	0.00064	0.00096	0.00066
A2	0.00059	0.00070	0.00117	0.00071
A3	0.00058	0.00069	0.00125	0.00070
A4	0.00058	0.00069	0.00125	0.00071

## Max Leakage Power (uW)

V1	V2	V3	V8
0.00277009	0.00764836	0.00998736	0.01883821

### Delay Table (ns)

Description	V1	V2	V3	V8
A1→ZN_FALL	0.01775	0.02234	0.01833	0.06085
A1→ZN_RISE	0.01768	0.01235	0.01087	0.03698
A2→ZN_FALL	0.02112	0.02578	0.02287	0.06428
A2→ZN_RISE	0.01966	0.01314	0.01252	0.03783
A3→ZN_FALL	0.02383	0.02859	0.02584	0.06707
A3→ZN_RISE	0.02212	0.01425	0.01384	0.03940
A4→ZN_FALL	0.02506	0.02973	0.02650	0.06817
A4→ZN_RISE	0.02444	0.01517	0.01476	0.04109

# LVT\_NOR2HS

## Cell Description

2-Input NOR

$$ZN = \neg(A1 \vee A2)$$



## Function Table

A1	A2	ZN
0	0	1
0	1	0
1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_NOR2HSV1	1.26	0.56
LVT_NOR2HSV2	1.26	0.56
LVT_NOR2HSV3	1.26	0.98
LVT_NOR2HSV8	1.26	1.68

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V8
A1	0.00028	0.00031	0.00043	0.00093
A2	0.00037	0.00040	0.00069	0.00151

## Pin Capacitance (pf)

Pin	V1	V2	V3	V8
A1	0.00059	0.00065	0.00100	0.00220
A2	0.00066	0.00070	0.00106	0.00240

## Max Leakage Power (uW)

V1	V2	V3	V8
0.00205445	0.00222182	0.00516162	0.01082784

## Delay Table (ns)

Description	V1	V2	V3	V8
-------------	----	----	----	----

A1→ZN_FALL	0.00975	0.00837	0.00721	0.00623
A1→ZN_RISE	0.01651	0.01745	0.01380	0.01141
A2→ZN_FALL	0.01058	0.00885	0.00823	0.00728
A2→ZN_RISE	0.01831	0.01918	0.01761	0.01475

# LVT\_NOR3HS

## Cell Description

3-Input NOR

$$Z_N = \neg(A_1 \vee A_2 \vee A_3)$$



## Function Table

A1	A2	A3	ZN
0	0	0	1
0	0	1	0
0	1	X	0
1	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_NOR3HSV1	1.26	0.84
LVT_NOR3HSV2	1.26	0.84
LVT_NOR3HSV3	1.26	1.26
LVT_NOR3HSV8	1.26	2.52

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V8
A1	0.00032	0.00041	0.00050	0.00117
A2	0.00039	0.00051	0.00068	0.00173
A3	0.00045	0.00060	0.00082	0.00221

## Pin Capacitance (pf)

Pin	V1	V2	V3	V8
A1	0.00051	0.00062	0.00091	0.00215
A2	0.00058	0.00068	0.00115	0.00233
A3	0.00059	0.00072	0.00123	0.00243

## Max Leakage Power (uW)

V1	V2	V3	V8
0.00366989	0.00401212	0.00718011	0.01460763

**Delay Table (ns)**

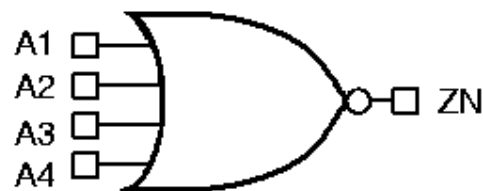
Description	V1	V2	V3	V8
A1→ZN_FALL	0.00981	0.00906	0.00764	0.00684
A1→ZN_RISE	0.03062	0.02713	0.02177	0.01698
A2→ZN_FALL	0.01052	0.00978	0.00866	0.00785
A2→ZN_RISE	0.03508	0.03155	0.02793	0.02365
A3→ZN_FALL	0.01077	0.01001	0.00898	0.00807
A3→ZN_RISE	0.03667	0.03339	0.02967	0.02619

# LVT\_NOR4HS

## Cell Description

4-Input NOR

$$ZN = \neg(A1 \vee A2 \vee A3 \vee A4)$$



## Function Table

A1	A2	A3	A4	ZN
0	0	0	0	1
0	0	0	1	0
0	0	1	X	0
0	1	X	X	0
1	X	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_NOR4HSV1	1.26	0.98
LVT_NOR4HSV2	1.26	0.98
LVT_NOR4HSV3	1.26	1.68
LVT_NOR4HSV8	1.26	2.10

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V8
A1	0.00037	0.00044	0.00063	0.00322
A2	0.00047	0.00054	0.00080	0.00333
A3	0.00058	0.00064	0.00097	0.00343
A4	0.00067	0.00073	0.00111	0.00354

## Pin Capacitance (pf)

Pin	V1	V2	V3	V8
A1	0.00056	0.00061	0.00091	0.00064
A2	0.00061	0.00067	0.00114	0.00066
A3	0.00063	0.00067	0.00126	0.00069
A4	0.00064	0.00070	0.00127	0.00071

## Max Leakage Power (uW)

V1	V2	V3	V8
0.00484253	0.00531252	0.01028217	0.01677953

### Delay Table (ns)

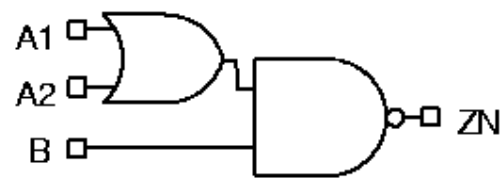
Description	V1	V2	V3	V8
A1→ZN_FALL	0.01072	0.00942	0.00835	0.03224
A1→ZN_RISE	0.03135	0.03584	0.03103	0.08274
A2→ZN_FALL	0.01171	0.01003	0.00917	0.03329
A2→ZN_RISE	0.03837	0.04259	0.03936	0.09029
A3→ZN_FALL	0.01240	0.01044	0.00974	0.03426
A3→ZN_RISE	0.04311	0.04743	0.04555	0.09511
A4→ZN_FALL	0.01250	0.01043	0.00978	0.03480
A4→ZN_RISE	0.04476	0.04915	0.04686	0.09792



# LVT\_OAI21HS

## Cell Description

2-1 OAI  
 $ZN = \neg((A1 \parallel A2) \& B)$



## Function Table

A1	A2	B	ZN
0	0	X	1
0	1	0	1
0	1	1	0
1	X	0	1
1	X	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_OAI21HSV1	1.26	0.84
LVT_OAI21HSV2	1.26	0.84

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00037	0.00049
A2	0.00044	0.00058
B	0.00026	0.00034

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00060	0.00070
A2	0.00061	0.00074
B	0.00056	0.00069

## Max Leakage Power (uW)

V1	V2
0.00234648	0.00333769

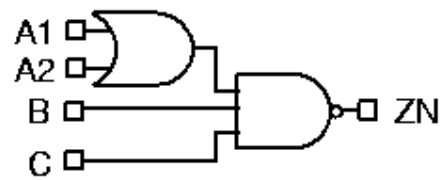
## Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.01582	0.01480
A1→ZN_RISE	0.02461	0.02240
A2→ZN_FALL	0.01743	0.01640
A2→ZN_RISE	0.02665	0.02452
B→ZN_FALL	0.01243	0.01149
B→ZN_RISE	0.01155	0.01053

# LVT\_OAI211HS

## Cell Description

2-1-1 OAI  
 $ZN = \neg((A1 \mid A2) \& B \& C)$



## Function Table

A1	A2	B	C	ZN
0	0	X	X	1
0	1	0	X	1
0	1	1	0	1
0	1	1	1	0
1	X	0	X	1
1	X	1	0	1
1	X	1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_OAI211HSV1	1.26	0.98
LVT_OAI211HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00051	0.00065
A2	0.00057	0.00074
B	0.00035	0.00044
C	0.00040	0.00052

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00053	0.00064
A2	0.00062	0.00075
B	0.00059	0.00071
C	0.00061	0.00074

## Max Leakage Power (uW)

V1	V2
0.00402503	0.00574641

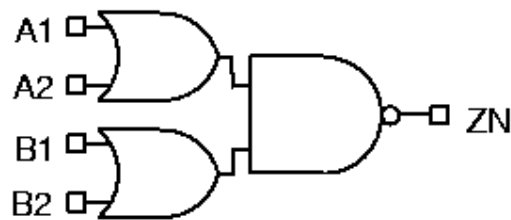
### Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.02497	0.02286
A1→ZN_RISE	0.02944	0.02630
A2→ZN_FALL	0.02729	0.02541
A2→ZN_RISE	0.03148	0.02851
B→ZN_FALL	0.01960	0.01764
B→ZN_RISE	0.01329	0.01183
C→ZN_FALL	0.02176	0.01995
C→ZN_RISE	0.01422	0.01277

# LVT\_OAI22HS

## Cell Description

2-2 OAI  
 $ZN = \neg((A1 \vee A2) \wedge (B1 \vee B2))$



## Function Table

A1	A2	B1	B2	ZN
0	0	X	X	1
0	1	0	0	1
0	1	0	1	0
0	1	1	X	0
1	X	0	0	1
1	X	0	1	0
1	X	1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_OAI22HSV1	1.26	0.98
LVT_OAI22HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00031	0.00038
A2	0.00038	0.00048
B1	0.00048	0.00062
B2	0.00055	0.00071

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00058	0.00069
A2	0.00055	0.00066
B1	0.00054	0.00065
B2	0.00061	0.00075

## Max Leakage Power (uW)

V1	V2
0.00297488	0.00425719

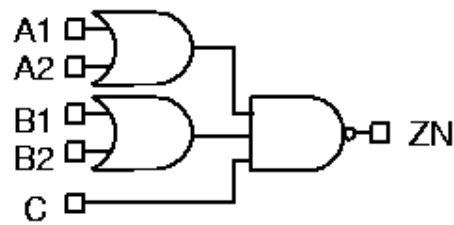
### Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.01344	0.01200
A1→ZN_RISE	0.02085	0.01790
A2→ZN_FALL	0.01505	0.01360
A2→ZN_RISE	0.02339	0.02039
B1→ZN_FALL	0.01766	0.01626
B1→ZN_RISE	0.02822	0.02523
B2→ZN_FALL	0.01898	0.01771
B2→ZN_RISE	0.03022	0.02749

# LVT\_OAI221HS

## Cell Description

2-2-1 OAI  
 $ZN = \neg((A1 \vee A2) \wedge (B1 \vee B2) \wedge C)$



## Function Table

A1	A2	B1	B2	C	ZN
0	0	X	X	X	1
0	1	0	0	X	1
0	1	0	1	0	1
0	1	0	1	1	0
0	1	1	X	0	1
0	1	1	X	1	0
1	X	0	0	X	1
1	X	0	1	0	1
1	X	0	1	1	0
1	X	1	X	0	1
1	X	1	X	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_OAI221HSV1	1.26	1.26
LVT_OAI221HSV2	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00050	0.00064
A2	0.00057	0.00074
B1	0.00067	0.00085
B2	0.00073	0.00094
C	0.00041	0.00052

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00055	0.00065
A2	0.00061	0.00073

B1	0.00057	0.00067
B2	0.00062	0.00074
C	0.00072	0.00088

### Max Leakage Power (uW)

V1	V2
0.00354444	0.00505340

### Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.02547	0.02339
A1→ZN_RISE	0.02879	0.02554
A2→ZN_FALL	0.02816	0.02623
A2→ZN_RISE	0.03127	0.02808
B1→ZN_FALL	0.02984	0.02746
B1→ZN_RISE	0.03505	0.03120
B2→ZN_FALL	0.03203	0.02991
B2→ZN_RISE	0.03688	0.03322
C→ZN_FALL	0.02161	0.01971
C→ZN_RISE	0.01509	0.01346

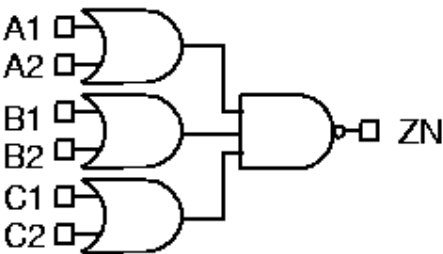


# LVT\_OAI222HS

## Cell Description

2-2-2 OAI

$$ZN = \neg((A1 \vee A2) \wedge (B1 \vee B2) \wedge (C1 \vee C2))$$



## Function Table

A1	A2	B1	B2	C1	C2	ZN
0	0	X	X	X	X	1
0	1	0	0	X	X	1
0	1	0	1	0	0	1
0	1	0	1	0	1	0
0	1	0	1	1	X	0
0	1	1	X	0	0	1
0	1	1	X	0	1	0
0	1	1	X	1	X	0
1	X	0	0	X	X	1
1	X	0	1	0	0	1
1	X	0	1	0	1	0
1	X	0	1	1	X	0
1	X	1	X	0	0	1
1	X	1	X	0	1	0
1	X	1	X	1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_OAI222HSV1	1.26	1.54
LVT_OAI222HSV2	1.26	1.54

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00061	0.00078
A2	0.00067	0.00086
B1	0.00076	0.00098
B2	0.00082	0.00108
C1	0.00044	0.00055
C2	0.00048	0.00062

### Pin Capacitance (pf)

Pin	V1	V2
A1	0.00059	0.00069
A2	0.00058	0.00070
B1	0.00055	0.00065
B2	0.00061	0.00074
C1	0.00073	0.00088
C2	0.00054	0.00066

### Max Leakage Power (uW)

V1	V2
0.00384486	0.00548614

### Delay Table (ns)

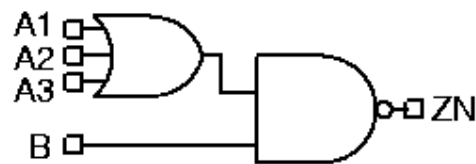
Description	V1	V2
A1→ZN_FALL	0.02758	0.02542
A1→ZN_RISE	0.03266	0.02918
A2→ZN_FALL	0.02948	0.02761
A2→ZN_RISE	0.03429	0.03105
B1→ZN_FALL	0.03141	0.02943
B1→ZN_RISE	0.03817	0.03469
B2→ZN_FALL	0.03336	0.03154
B2→ZN_RISE	0.04006	0.03677
C1→ZN_FALL	0.02186	0.01948
C1→ZN_RISE	0.02640	0.02284
C2→ZN_FALL	0.02201	0.01998
C2→ZN_RISE	0.02701	0.02377

# LVT\_OAI31HS

## Cell Description

3-1 OAI

$$ZN = \neg((A1 \mid A2 \mid A3) \& B)$$



## Function Table

A1	A2	A3	B	ZN
0	0	0	X	1
0	0	1	0	1
0	0	1	1	0
0	1	X	0	1
0	1	X	1	0
1	X	X	0	1
1	X	X	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_OAI31HSV1	1.26	0.98
LVT_OAI31HSV2	1.26	0.98

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00039	0.00052
A2	0.00046	0.00061
A3	0.00053	0.00070
B	0.00029	0.00037

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00055	0.00069
A2	0.00056	0.00068
A3	0.00061	0.00075
B	0.00056	0.00069

## Max Leakage Power (uW)

V1	V2
0.00253953	0.00362056

### **Delay Table (ns)**

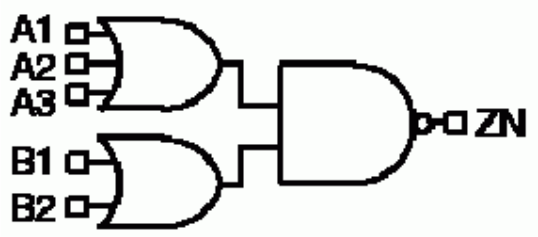
Description	V1	V2
A1→ZN_FALL	0.01642	0.01533
A1→ZN_RISE	0.03586	0.03255
A2→ZN_FALL	0.01805	0.01688
A2→ZN_RISE	0.04004	0.03667
A3→ZN_FALL	0.01884	0.01763
A3→ZN_RISE	0.04178	0.03847
B→ZN_FALL	0.01237	0.01131
B→ZN_RISE	0.01178	0.01054

# LVT\_OAI32HS

## Cell Description

3-2 OAI

$$ZN = \neg((A1 \vee A2 \vee A3) \wedge (B1 \vee B2))$$



## Function Table

A1	A2	A3	B1	B2	ZN
0	0	0	X	X	1
0	0	1	0	0	1
0	0	1	0	1	0
0	0	1	1	X	0
0	1	X	0	0	1
0	1	X	0	1	0
0	1	X	1	X	0
1	X	X	0	0	1
1	X	X	0	1	0
1	X	X	1	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_OAI32HSV1	1.26	1.12
LVT_OAI32HSV2	1.26	1.12

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00039	0.00048
A2	0.00045	0.00057
A3	0.00054	0.00068
B1	0.00059	0.00074
B2	0.00066	0.00084

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00055	0.00065
A2	0.00055	0.00066
A3	0.00058	0.00070

B1	0.00054	0.00064
B2	0.00062	0.00075

### Max Leakage Power (uW)

V1	V2
0.00345505	0.00465868

### Delay Table (ns)

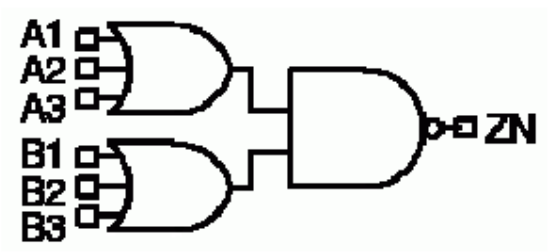
Description	V1	V2
A1→ZN_FALL	0.01481	0.01327
A1→ZN_RISE	0.03290	0.02810
A2→ZN_FALL	0.01642	0.01498
A2→ZN_RISE	0.03734	0.03275
A3→ZN_FALL	0.01813	0.01650
A3→ZN_RISE	0.04110	0.03610
B1→ZN_FALL	0.01892	0.01732
B1→ZN_RISE	0.03220	0.02855
B2→ZN_FALL	0.02034	0.01887
B2→ZN_RISE	0.03431	0.03088

# LVT\_OAI33HS

## Cell Description

3-3 OAI

$$ZN = \neg((A1 \vee A2 \vee A3) \wedge (B1 \vee B2 \vee B3))$$



## Function Table

A1	A2	A3	B1	B2	B3	ZN
0	0	0	X	X	X	1
0	0	1	0	0	0	1
0	0	1	0	0	1	0
0	0	1	0	1	X	0
0	0	1	1	X	X	0
0	1	X	0	0	0	1
0	1	X	0	0	1	0
0	1	X	0	1	X	0
0	1	X	1	X	X	0
1	X	X	0	0	0	1
1	X	X	0	0	1	0
1	X	X	0	1	X	0
1	X	X	1	X	X	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_OAI33HSV1	1.26	1.26
LVT_OAI33HSV2	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00061	0.00076
A2	0.00068	0.00086
A3	0.00075	0.00095
B1	0.00040	0.00050
B2	0.00047	0.00059
B3	0.00055	0.00070

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00053	0.00063
A2	0.00061	0.00073
A3	0.00062	0.00074
B1	0.00057	0.00068
B2	0.00056	0.00067
B3	0.00057	0.00068

### Max Leakage Power (uW)

V1	V2
0.00349411	0.00502011

### Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.01933	0.01760
A1→ZN_RISE	0.04750	0.04179
A2→ZN_FALL	0.02082	0.01920
A2→ZN_RISE	0.05180	0.04640
A3→ZN_FALL	0.02188	0.02015
A3→ZN_RISE	0.05384	0.04819
B1→ZN_FALL	0.01438	0.01295
B1→ZN_RISE	0.03284	0.02797
B2→ZN_FALL	0.01595	0.01453
B2→ZN_RISE	0.03753	0.03273
B3→ZN_FALL	0.01734	0.01574
B3→ZN_RISE	0.04054	0.03533



# LVT\_OR2HS

## Cell Description

2-Input OR

$Z=(A1\text{I}A2)$



## Function Table

A1	A2	Z
0	0	0
0	1	1
1	X	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_OR2HSV1	1.26	0.84
LVT_OR2HSV2	1.26	0.84
LVT_OR2HSV8	1.26	1.26

## Pin Power (uW/MHz)

Pin	V1	V2	V8
A1	0.00064	0.00074	0.00224
A2	0.00071	0.00080	0.00234

## Pin Capacitance (pf)

Pin	V1	V2	V8
A1	0.00049	0.00048	0.00068
A2	0.00051	0.00051	0.00074

## Max Leakage Power (uW)

V1	V2	V8
0.00254751	0.00271990	0.01120697

## Delay Table (ns)

Description	V1	V2	V8
A1→Z_FALL	0.03846	0.04009	0.04721

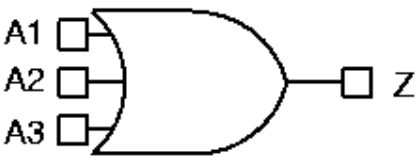
A1→Z_RISE	0.02305	0.02284	0.02291
A2→Z_FALL	0.04246	0.04381	0.04989
A2→Z_RISE	0.02482	0.02444	0.02402

# LVT\_OR3HS

## Cell Description

3-Input OR

$Z=(A1|A2|A3)$



## Function Table

A1	A2	A3	Z
0	0	0	0
0	0	1	1
0	1	X	1
1	X	X	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_OR3HSV1	1.26	0.98
LVT_OR3HSV2	1.26	0.98
LVT_OR3HSV8	1.26	1.54

## Pin Power (uW/MHz)

Pin	V1	V2	V8
A1	0.00078	0.00089	0.00262
A2	0.00088	0.00099	0.00272
A3	0.00099	0.00110	0.00283

## Pin Capacitance (pf)

Pin	V1	V2	V8
A1	0.00056	0.00057	0.00065
A2	0.00060	0.00060	0.00070
A3	0.00063	0.00064	0.00072

## Max Leakage Power (uW)

V1	V2	V8
0.00371385	0.00417243	0.01355793

## Delay Table (ns)

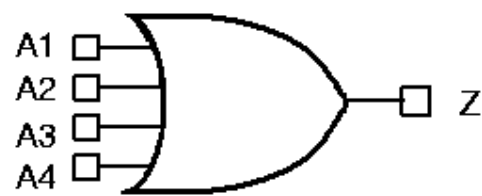
Description	V1	V2	V8
A1→Z_FALL	0.03860	0.04006	0.06958
A1→Z_RISE	0.02689	0.02667	0.02407
A2→Z_FALL	0.04307	0.04459	0.07405
A2→Z_RISE	0.02903	0.02881	0.02487
A3→Z_FALL	0.04624	0.04764	0.07685
A3→Z_RISE	0.03132	0.03106	0.02585

# LVT\_OR4HS

## Cell Description

4-Input OR

$Z=(A1|A2|A3|A4)$



## Function Table

A1	A2	A3	A4	Z
0	0	0	0	0
0	0	0	1	1
0	0	1	X	1
0	1	X	X	1
1	X	X	X	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_OR4HSV1	1.26	1.12
LVT_OR4HSV2	1.26	1.12
LVT_OR4HSV8	1.26	1.68

## Pin Power (uW/MHz)

Pin	V1	V2	V8
A1	0.00082	0.00091	0.00286
A2	0.00093	0.00102	0.00296
A3	0.00102	0.00111	0.00307
A4	0.00113	0.00122	0.00318

## Pin Capacitance (pf)

Pin	V1	V2	V8
A1	0.00056	0.00056	0.00065
A2	0.00061	0.00058	0.00068
A3	0.00059	0.00060	0.00068
A4	0.00062	0.00062	0.00072

## Max Leakage Power (uW)

V1	V2	V8
----	----	----

0.00439931	0.00489348	0.01498753
------------	------------	------------

### Delay Table (ns)

Description	V1	V2	V8
A1→Z_FALL	0.04841	0.04921	0.08932
A1→Z_RISE	0.02803	0.02708	0.02422
A2→Z_FALL	0.05655	0.05695	0.09706
A2→Z_RISE	0.03047	0.02943	0.02512
A3→Z_FALL	0.06025	0.06129	0.10138
A3→Z_RISE	0.03211	0.03142	0.02592
A4→Z_FALL	0.06402	0.06450	0.10480
A4→Z_RISE	0.03394	0.03291	0.02673

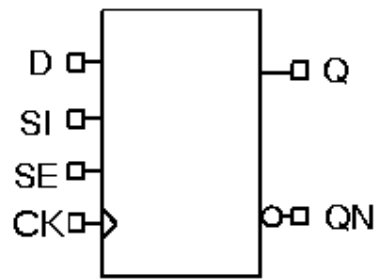
# LVT\_SDHS

## Cell Description

Scan D Flip-Flop

Q = rising (CK) ? (SE&SI | !SE&D) : pre\_Q

QN = !Q



## Function Table

CK<1>	CK	SE	SI	D	Q
0	0	X	X	X	Q<1>
0	1	0	X	0	0
0	1	0	X	1	1
0	1	1	0	X	0
0	1	1	1	X	1
1	X	X	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_SDHSV1	1.26	4.20
LVT_SDHSV2	1.26	4.06

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00158	0.00158
D	0.00035	0.00035
Q	0.00095	0.00105
QN	0.00096	0.00106
SE	0.00073	0.00073
SI	0.00040	0.00040

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00047	0.00047
D	0.00050	0.00050
SE	0.00105	0.00105
SI	0.00039	0.00039

### Max Leakage Power (uW)

V1	V2
0.00670136	0.00705864

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.08662	0.08767
CK→Q_RISE	0.08397	0.08575
CK→QN_FALL	0.06365	0.06416
CK→QN_RISE	0.07119	0.07058

### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.00857	-0.00857
D	hold_RISE→CK	-0.03150	-0.02863
D	setup_FALL→CK	0.03148	0.03148
D	setup_RISE→CK	0.04295	0.04295
SE	hold_FALL→CK	-0.01716	-0.01431
SE	hold_RISE→CK	-0.03721	-0.03721
SE	setup_FALL→CK	0.04294	0.04294
SE	setup_RISE→CK	0.05152	0.05439
SI	hold_FALL→CK	-0.03721	-0.03434
SI	hold_RISE→CK	-0.04294	-0.04009
SI	setup_FALL→CK	0.06583	0.06583
SI	setup_RISE→CK	0.05439	0.05726
CK	minpwh	0.06502	0.07137
CK	minpwl	0.10155	0.10555

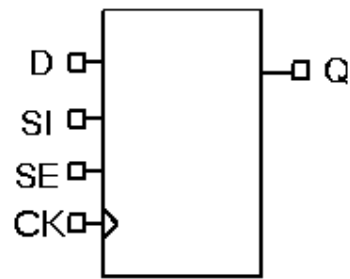


# LVT\_SDQHS

## Cell Description

Scan D Flip-Flop

Q = rising (CK) ? (SE&SI | !SE&D) : pre\_Q



## Function Table

CK<1>	CK	SE	D	SI	Q
0	0	X	X	X	Q<1>
0	1	0	0	X	0
0	1	0	1	X	1
0	1	1	X	0	0
0	1	1	X	1	1
1	X	X	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_SDQHSV1	1.26	4.06
LVT_SDQHSV2	1.26	4.06

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00152	0.00152
D	0.00034	0.00034
Q	0.00144	0.00155
SE	0.00072	0.00072
SI	0.00039	0.00039

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00047	0.00047
D	0.00051	0.00051
SE	0.00104	0.00105
SI	0.00039	0.00040

## Max Leakage Power (uW)

V1	V2
0.00555794	0.00565766

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.08117	0.08120
CK→Q_RISE	0.07740	0.07688

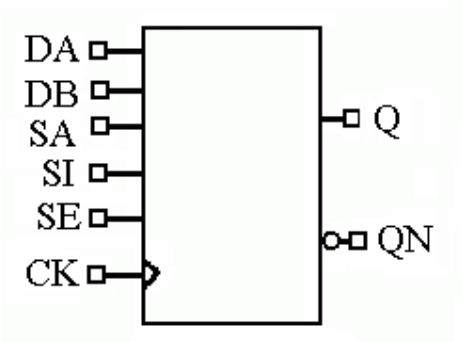
### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.01144	-0.01144
D	hold_RISE→CK	-0.02863	-0.02863
D	setup_FALL→CK	0.03148	0.03148
D	setup_RISE→CK	0.03722	0.04009
SE	hold_FALL→CK	-0.01717	-0.01431
SE	hold_RISE→CK	-0.04007	-0.04006
SE	setup_FALL→CK	0.04008	0.04293
SE	setup_RISE→CK	0.05153	0.05438
SI	hold_FALL→CK	-0.04007	-0.03720
SI	hold_RISE→CK	-0.04294	-0.04294
SI	setup_FALL→CK	0.06298	0.06583
SI	setup_RISE→CK	0.05439	0.05726
CK	minpwh	0.04602	0.04602
CK	minpwl	0.09362	0.09362

# LVT\_SDVHS

## Cell Description

Scan D Flip-Flop with Mux Inputs  
 $Q = \text{rising}(CK) ? (SE \& SI \mid !SE \& (DA \& SA \mid DB \& !SA)) :$   
pre\_Q  
QN = !Q



## Function Table

CK<1>	CK	SA	DB	DA	SE	SI	Q
0	0	X	X	X	X	X	Q<1>
0	1	0	0	X	0	X	0
0	1	0	0	X	1	0	0
0	1	0	0	X	1	1	1
0	1	0	1	X	0	X	1
0	1	0	1	X	1	0	0
0	1	0	1	X	1	1	1
0	1	1	X	0	0	X	0
0	1	1	X	0	1	0	0
0	1	1	X	0	1	1	1
0	1	1	X	1	0	X	1
0	1	1	X	1	1	0	0
0	1	1	X	1	1	1	1
1	X	X	X	X	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_SDVHSV1	1.26	5.32
LVT_SDVHSV2	1.26	5.32

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00134	0.00134
DA	0.00020	0.00020
DB	0.00020	0.00020
Q	0.00094	0.00104
QN	0.00094	0.00105
SA	0.00054	0.00054
SE	0.00082	0.00082
SI	0.00045	0.00045

### Pin Capacitance (pf)

Pin	V1	V2
CK	0.00046	0.00046
DA	0.00046	0.00046
DB	0.00104	0.00104
SA	0.00097	0.00097
SE	0.00110	0.00110
SI	0.00042	0.00042

### Max Leakage Power (uW)

V1	V2
0.00772587	0.00828107

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.08211	0.08336
CK→Q_RISE	0.08087	0.08236
CK→QN_FALL	0.06114	0.06129
CK→QN_RISE	0.06675	0.06550

### Timing Constraints (ns)

Pin	Requirement	V1	V2
DA	hold_FALL→CK	-0.02003	-0.02003
DA	hold_RISE→CK	-0.03720	-0.03720
DA	setup_FALL→CK	0.04292	0.04579
DA	setup_RISE→CK	0.04578	0.04866
DB	hold_FALL→CK	-0.02290	-0.02005
DB	hold_RISE→CK	-0.03721	-0.03433
DB	setup_FALL→CK	0.04580	0.04580
DB	setup_RISE→CK	0.04579	0.04579
SA	hold_FALL→CK	-0.04292	-0.04292
SA	hold_RISE→CK	-0.02290	-0.02290
SA	setup_FALL→CK	0.05439	0.05438
SA	setup_RISE→CK	0.04581	0.04865
SE	hold_FALL→CK	-0.01431	-0.01144
SE	hold_RISE→CK	-0.04293	-0.04007
SE	setup_FALL→CK	0.04293	0.04293
SE	setup_RISE→CK	0.05725	0.05725
SI	hold_FALL→CK	-0.04006	-0.03720
SI	hold_RISE→CK	-0.04581	-0.04581
SI	setup_FALL→CK	0.06869	0.06869
SI	setup_RISE→CK	0.06011	0.06302

CK	minpwh	0.06501	0.06819
CK	minpwl	0.09357	0.09355

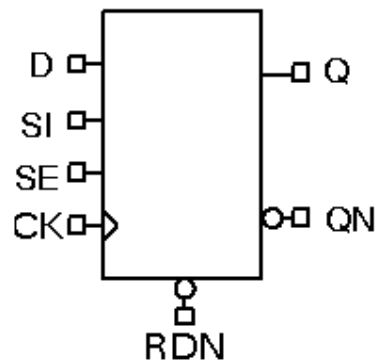
# LVT\_SDRNHS

## Cell Description

Scan D Flip-Flop with Async Clear

$Q = \text{!RDN} ? 0 : \text{rising}(\text{CK}) ? (\text{SE} \& \text{SI} \mid \text{!SE} \& \text{D}) : \text{pre\_Q}$

$\text{QN} = \text{!Q}$



## Function Table

RDN	CK<1>	CK	SE	SI	D	Q
0	X	X	X	X	X	0
1	0	0	X	X	X	Q<1>
1	0	1	0	X	0	0
1	0	1	0	X	1	1
1	0	1	1	0	X	0
1	0	1	1	1	X	1
1	1	X	X	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_SDRNHSV1	1.26	5.04
LVT_SDRNHSV2	1.26	5.04

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00176	0.00176
D	0.00021	0.00021
Q	0.00119	0.00129
QN	0.00123	0.00133
RDN	0.00048	0.00048
SE	0.00052	0.00052
SI	0.00025	0.00025

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00047	0.00047
D	0.00041	0.00040
RDN	0.00180	0.00180
SE	0.00084	0.00084

SI	0.00035	0.00036
----	---------	---------

### Max Leakage Power (uW)

V1	V2
0.00903607	0.00948114

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.08683	0.08798
CK→Q_RISE	0.09246	0.09466
RDN→Q_FALL	0.02375	0.02362
CK→QN_FALL	0.06369	0.06467
CK→QN_RISE	0.07097	0.07039
RDN→QN_RISE	0.07195	0.07264

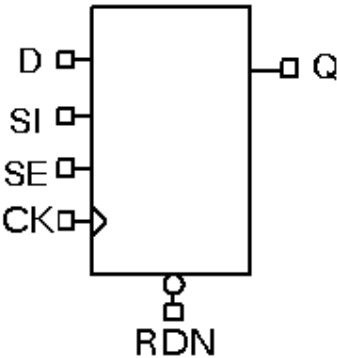
### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.02005	-0.01719
D	hold_RISE→CK	-0.04867	-0.04579
D	setup_FALL→CK	0.05440	0.05726
D	setup_RISE→CK	0.07157	0.07156
RDN	setup_RISE→CK	0.08874	0.09159
RDN	hold_RISE→CK	-0.08015	-0.08016
SE	hold_FALL→CK	-0.02576	-0.02290
SE	hold_RISE→CK	-0.05152	-0.04867
SE	setup_FALL→CK	0.07156	0.07443
SE	setup_RISE→CK	0.07728	0.07729
SI	hold_FALL→CK	-0.04008	-0.03723
SI	hold_RISE→CK	-0.05725	-0.05724
SI	setup_FALL→CK	0.08302	0.08303
SI	setup_RISE→CK	0.08303	0.08588
CK	minpwh	0.06826	0.07140
CK	minpwl	0.11744	0.11741
RDN	minpwl	0.04602	0.04604

# LVT\_SDRNQHS

## Cell Description

Scan D Flip-Flop with Async Clear  
 $Q = \text{!RDN} ? 0 : \text{rising (CK)} ? (\text{SE} \& \text{SI} \mid \text{!SE} \& \text{D}) : \text{pre\_Q}$



## Function Table

RDN	CK<1>	CK	SE	D	SI	Q
0	X	X	X	X	X	0
1	0	0	X	X	X	Q<1>
1	0	1	0	0	X	0
1	0	1	0	1	X	1
1	0	1	1	X	0	0
1	0	1	1	X	1	1
1	1	X	X	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_SDRNQHSV1	1.26	4.76
LVT_SDRNQHSV2	1.26	4.76

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00172	0.00172
D	0.00021	0.00021
Q	0.00189	0.00197
RDN	0.00047	0.00047
SE	0.00057	0.00057
SI	0.00024	0.00024

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00048	0.00048
D	0.00042	0.00042
RDN	0.00166	0.00166
SE	0.00109	0.00109
SI	0.00036	0.00036



### Max Leakage Power (uW)

V1	V2
0.00699163	0.00720967

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.08295	0.08279
CK→Q_RISE	0.08037	0.07979
RDN→Q_FALL	0.04032	0.04091

### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.02291	-0.02005
D	hold_RISE→CK	-0.04580	-0.04580
D	setup_FALL→CK	0.04867	0.04867
D	setup_RISE→CK	0.06297	0.06583
RDN	setup_RISE→CK	0.08586	0.08875
RDN	hold_RISE→CK	-0.08015	-0.08016
SE	hold_FALL→CK	-0.02863	-0.02577
SE	hold_RISE→CK	-0.05727	-0.05727
SE	setup_FALL→CK	0.05726	0.06011
SE	setup_RISE→CK	0.07730	0.08016
SI	hold_FALL→CK	-0.04867	-0.04579
SI	hold_RISE→CK	-0.06299	-0.06299
SI	setup_FALL→CK	0.07729	0.07730
SI	setup_RISE→CK	0.08017	0.08303
CK	minpwh	0.04600	0.04600
CK	minpwl	0.10950	0.11342
RDN	minpwl	0.05555	0.05870

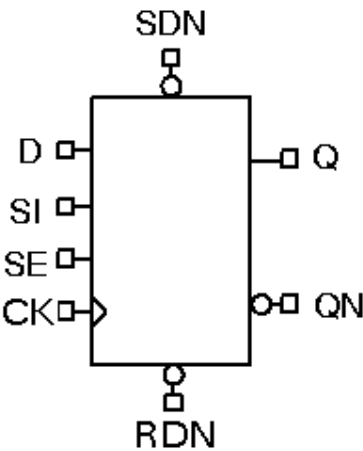
# LVT\_SDRSNHS

## Cell Description

Scan D Flip-Flop with Async Clear and Set

$Q = !SDN \text{ ? } 1 : !RDN \text{ ? } 0 : \text{rising (CK) ? (SE\&SI} \\ | !SE\&D) : \text{pre\_Q}$

$QN = !Q$



## Function Table

RDN	SDN	CK<1>	CK	SE	D	SI	Q
0	0	X	X	X	X	X	1
0	1	X	X	X	X	X	0
1	0	X	X	X	X	X	1
1	1	0	0	X	X	X	Q<1>
1	1	0	1	0	0	X	0
1	1	0	1	0	1	X	1
1	1	0	1	1	X	0	0
1	1	0	1	1	X	1	1
1	1	1	X	X	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_SDRSNHSV1	1.26	7.14
LVT_SDRSNHSV2	1.26	7.14

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00220	0.00220
D	0.00019	0.00019
Q	0.00140	0.00148
QN	0.00140	0.00150
RDN	0.00110	0.00110
SDN	0.00019	0.00019
SE	0.00055	0.00055
SI	0.00022	0.00022

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00065	0.00065

D	0.00050	0.00050
RDN	0.00114	0.00114
SDN	0.00089	0.00089
SE	0.00099	0.00099
SI	0.00041	0.00041

### Max Leakage Power (uW)

V1	V2
0.00758988	0.00830893

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.11238	0.11257
CK→Q_RISE	0.10200	0.10259
RDN→Q_FALL	0.10055	0.10067
SDN→Q_FALL	0.07214	0.07229
SDN→Q_RISE	0.07530	0.07549
CK→QN_FALL	0.08304	0.08153
CK→QN_RISE	0.09148	0.08988
RDN→QN_RISE	0.07967	0.07806
SDN→QN_FALL	0.05649	0.05451
SDN→QN_RISE	0.05119	0.04957

### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.01432	-0.01145
D	hold_RISE→CK	-0.06298	-0.06012
D	setup_FALL→CK	0.05727	0.05727
D	setup_RISE→CK	0.08301	0.08589
RDN	setup_RISE→CK	0.10018	0.10305
RDN	hold_RISE→CK	-0.08873	-0.08873
SDN	setup_RISE→CK	-0.04865	-0.04580
SDN	hold_RISE→CK	0.06296	0.06296
SDN	non_seq_hold_RISE→RDN	-0.03436	-0.03436
SDN	non_seq_setup_RISE→RDN	0.04009	0.04580
SE	hold_FALL→CK	-0.01715	-0.01429
SE	hold_RISE→CK	-0.06584	-0.06584
SE	setup_FALL→CK	0.06868	0.07155
SE	setup_RISE→CK	0.09161	0.09445
SI	hold_FALL→CK	-0.02864	-0.02577
SI	hold_RISE→CK	-0.07727	-0.07727
SI	setup_FALL→CK	0.06870	0.07157
SI	setup_RISE→CK	0.10017	0.10305

CK	minpwh	0.08725	0.09044
CK	minpwl	0.13727	0.14122
RDN	minpwl	0.06820	0.07139
SDN	minpwl	0.09038	0.09672

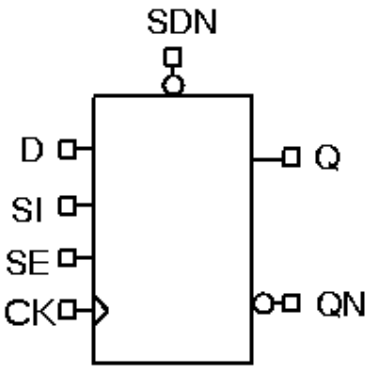
# LVT\_SDSNHS

## Cell Description

Scan D Flip-Flop with Async Set

$Q = !SDN ? 1 : \text{rising}(CK) ? (SE \& SI \mid !SE \& D) : \text{pre\_}Q$

$QN = !Q$



## Function Table

SDN	CK<1>	CK	SE	SI	D	Q
0	X	X	X	X	X	1
1	0	0	X	X	X	Q<1>
1	0	1	0	X	0	0
1	0	1	0	X	1	1
1	0	1	1	0	X	0
1	0	1	1	1	X	1
1	1	X	X	X	X	Q<1>

## Cell Size

CellName	Height(um)	Width(um)
LVT_SDSNHSV1	1.26	4.76
LVT_SDSNHSV2	1.26	4.76

## Pin Power (uW/MHz)

Pin	V1	V2
CK	0.00173	0.00174
D	0.00028	0.00028
Q	0.00123	0.00132
QN	0.00123	0.00134
SDN	0.00014	0.00014
SE	0.00060	0.00061
SI	0.00032	0.00032

## Pin Capacitance (pf)

Pin	V1	V2
CK	0.00048	0.00048
D	0.00050	0.00051
SDN	0.00093	0.00094
SE	0.00097	0.00097

SI	0.00038	0.00038
----	---------	---------

### Max Leakage Power (uW)

V1	V2
0.00776924	0.00803439

### Delay Table (ns)

Description	V1	V2
CK→Q_FALL	0.09616	0.09695
CK→Q_RISE	0.09150	0.09281
SDN→Q_RISE	0.07264	0.07364
CK→QN_FALL	0.07340	0.07222
CK→QN_RISE	0.07759	0.07705
SDN→QN_FALL	0.05491	0.05347

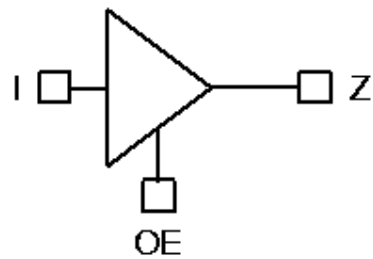
### Timing Constraints (ns)

Pin	Requirement	V1	V2
D	hold_FALL→CK	-0.01145	-0.00858
D	hold_RISE→CK	-0.02864	-0.02864
D	setup_FALL→CK	0.03720	0.03721
D	setup_RISE→CK	0.04295	0.04295
SDN	setup_RISE→CK	-0.03722	-0.03435
SDN	hold_RISE→CK	0.04294	0.04294
SE	hold_FALL→CK	-0.01431	-0.01431
SE	hold_RISE→CK	-0.04007	-0.03722
SE	setup_FALL→CK	0.04578	0.04866
SE	setup_RISE→CK	0.05438	0.05439
SI	hold_FALL→CK	-0.03722	-0.03436
SI	hold_RISE→CK	-0.04295	-0.04294
SI	setup_FALL→CK	0.06585	0.06871
SI	setup_RISE→CK	0.06012	0.06012
CK	minpwh	0.07774	0.08408
CK	minpwl	0.10949	0.10949
SDN	minpwl	0.08090	0.08725

# LVT\_TBUFHS

## Cell Description

3-State Buffer with High Enable  
Z=!OE ? I:(1'bZ)



## Function Table

OE	I	Z
0	X	Z
1	0	0
1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_TBUFHSV1	1.26	1.26
LVT_TBUFHSV2	1.26	1.54
LVT_TBUFHSV3	1.26	1.54
LVT_TBUFHSV6	1.26	1.82
LVT_TBUFHSV8	1.26	2.10
LVT_TBUFHSV12	1.26	2.52
LVT_TBUFHSV16	1.26	2.94
LVT_TBUFHSV20	1.26	3.50
LVT_TBUFHSV24	1.26	4.06

## Pin Power (uW/MHz)

Pin	V1	V2	V3	V6	V8	V12	V16	V20
I	0.00089	0.00110	0.00123	0.00192	0.00237	0.00330	0.00411	0.00528
OE	0.00060	0.00079	0.00091	0.00152	0.00191	0.00270	0.00338	0.00430

Pin	V24
I	0.00657
OE	0.00530

## Pin Capacitance (pf)

Pin	V1	V2	V3	V6	V8	V12	V16	V20
I	0.00050	0.00047	0.00047	0.00048	0.00047	0.00050	0.00047	0.00049
OE	0.00093	0.00091	0.00091	0.00092	0.00091	0.00093	0.00092	0.00093

Pin	V24
I	0.00048
OE	0.00093

### Max Leakage Power (uW)

V1	V2	V3	V6	V8	V12	V16	V20
0.00267368	0.00393795	0.00496000	0.00877629	0.01166890	0.01796069	0.02412397	0.03079030

V24
0.03866697

### Delay Table (ns)

Description	V1	V2	V3	V6	V8	V12	V16	V20
I→Z_FALL	0.04645	0.04606	0.04707	0.05878	0.06525	0.08178	0.09375	0.11001
I→Z_RISE	0.03931	0.03787	0.03803	0.04642	0.05137	0.06346	0.07208	0.08367
OE→Z_FALL	0.02763	0.02710	0.02730	0.03210	0.03478	0.04157	0.04655	0.05319
OE→Z_RISE	0.02797	0.02749	0.02757	0.03175	0.03417	0.03986	0.04367	0.04886

Description	V24
I→Z_FALL	0.12742
I→Z_RISE	0.09570
OE→Z_FALL	0.06042
OE→Z_RISE	0.05443



# LVT\_XNOR2HS

## Cell Description

2-Input Exclusive NOR

$ZN = \neg(A1 \oplus A2)$



## Function Table

A2	A1	ZN
0	0	1
0	1	0
1	0	0
1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_XNOR2HSV1	1.26	1.96
LVT_XNOR2HSV2	1.26	1.96

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00113	0.00120
A2	0.00189	0.00199

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00104	0.00105
A2	0.00067	0.00066

## Max Leakage Power (uW)

V1	V2
0.00455746	0.00461396

## Delay Table (ns)

Description	V1	V2
A1→ZN_FALL	0.03211	0.03262

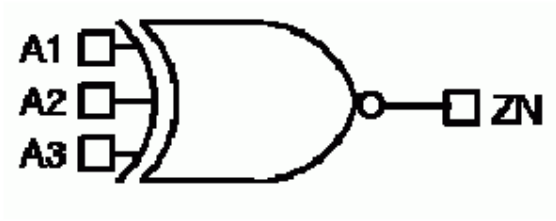
A1→ZN_RISE	0.03351	0.03297
A2→ZN_FALL	0.05161	0.05246
A2→ZN_RISE	0.04912	0.04878

# LVT\_XNOR3HS

## Cell Description

3-Input Exclusive NOR

$$ZN = \neg(A1 \oplus A2 \oplus A3)$$



## Function Table

A2	A1	A3	ZN
0	0	0	1
0	0	1	0
0	1	0	0
0	1	1	1
1	0	0	0
1	0	1	1
1	1	0	1
1	1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_XNOR3HSV1	1.26	3.08
LVT_XNOR3HSV2	1.26	3.08

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00311	0.00315
A2	0.00225	0.00229
A3	0.00106	0.00109

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00067	0.00067
A2	0.00105	0.00105
A3	0.00103	0.00104

## Max Leakage Power (uW)

V1	V2
----	----

0.00999257	0.01011306
------------	------------

### Delay Table (ns)

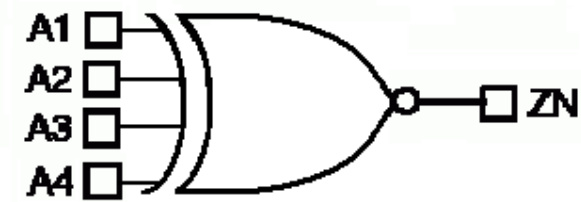
Description	V1	V2
A1→ZN_FALL	0.08144	0.08306
A1→ZN_RISE	0.08020	0.07909
A2→ZN_FALL	0.06316	0.06468
A2→ZN_RISE	0.06121	0.06007
A3→ZN_FALL	0.03149	0.03263
A3→ZN_RISE	0.03047	0.02956

# LVT\_XNOR4HS

## Cell Description

4-Input Exclusive NOR

$$ZN = \neg(A1 \oplus A2 \oplus A3 \oplus A4)$$



## Function Table

A2	A1	A3	A4	ZN
0	0	0	0	1
0	0	0	1	0
0	0	1	0	0
0	0	1	1	1
0	1	0	0	0
0	1	0	1	1
0	1	1	0	1
0	1	1	1	0
1	0	0	0	0
1	0	0	1	1
1	0	1	0	1
1	0	1	1	0
1	1	0	0	1
1	1	0	1	0
1	1	1	0	0
1	1	1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_XNOR4HSV1	1.26	5.46
LVT_XNOR4HSV2	1.26	5.46

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00327	0.00335
A2	0.00400	0.00407
A3	0.00281	0.00280
A4	0.00350	0.00346

### Pin Capacitance (pf)

Pin	V1	V2
A1	0.00104	0.00106
A2	0.00067	0.00068
A3	0.00109	0.00109
A4	0.00067	0.00067

### Max Leakage Power (uW)

V1	V2
0.01249909	0.01304464

### Delay Table (ns)

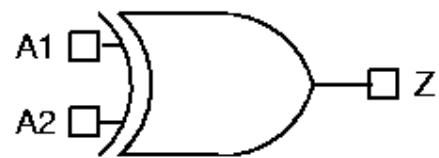
Description	V1	V2
A1→ZN_FALL	0.08784	0.08637
A1→ZN_RISE	0.08604	0.08490
A2→ZN_FALL	0.10612	0.10446
A2→ZN_RISE	0.10432	0.10298
A3→ZN_FALL	0.07401	0.07259
A3→ZN_RISE	0.07595	0.07353
A4→ZN_FALL	0.09188	0.09024
A4→ZN_RISE	0.09389	0.09121

# LVT\_XOR2HS

## Cell Description

2-Input Exclusive OR

$Z=(A1\wedge A2)$



## Function Table

A2	A1	Z
0	0	0
0	1	1
1	0	1
1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_XOR2HSV1	1.26	1.96
LVT_XOR2HSV2	1.26	1.96

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00112	0.00120
A2	0.00187	0.00195

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00104	0.00103
A2	0.00067	0.00067

## Max Leakage Power (uW)

V1	V2
0.00483773	0.00483708

## Delay Table (ns)

Description	V1	V2
A1→Z_FALL	0.03218	0.03285

A1→Z_RISE	0.03327	0.03292
A2→Z_FALL	0.05140	0.05205
A2→Z_RISE	0.04908	0.04866

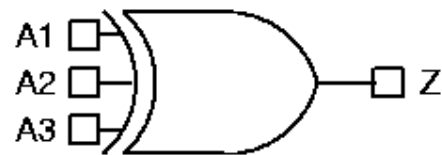


# LVT\_XOR3HS

## Cell Description

3-Input Exclusive OR

$$Z=(A1^A2^A3)$$



## Function Table

A2	A1	A3	Z
0	0	0	0
0	0	1	1
0	1	0	1
0	1	1	0
1	0	0	1
1	0	1	0
1	1	0	0
1	1	1	1

## Cell Size

CellName	Height(um)	Width(um)
LVT_XOR3HSV1	1.26	3.08
LVT_XOR3HSV2	1.26	3.08

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00317	0.00322
A2	0.00230	0.00235
A3	0.00104	0.00108

## Pin Capacitance (pf)

Pin	V1	V2
A1	0.00067	0.00067
A2	0.00105	0.00105
A3	0.00102	0.00102

## Max Leakage Power (uW)

V1	V2
----	----

0.01023824	0.01023774
------------	------------

### Delay Table (ns)

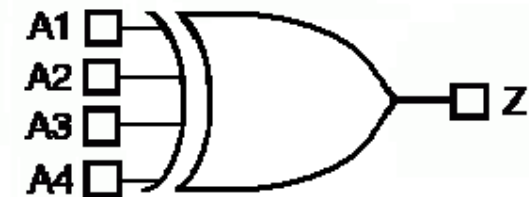
Description	V1	V2
A1→Z_FALL	0.08410	0.08567
A1→Z_RISE	0.08115	0.07973
A2→Z_FALL	0.06571	0.06722
A2→Z_RISE	0.06224	0.06082
A3→Z_FALL	0.02968	0.03090
A3→Z_RISE	0.03032	0.02903

# LVT\_XOR4HS

## Cell Description

4-Input Exclusive OR

$$Z=(A1\wedge A2\wedge A3\wedge A4)$$



## Function Table

A2	A1	A3	A4	Z
0	0	0	0	0
0	0	0	1	1
0	0	1	0	1
0	0	1	1	0
0	1	0	0	1
0	1	0	1	0
0	1	1	0	0
0	1	1	1	1
1	0	0	0	1
1	0	0	1	0
1	0	1	0	0
1	0	1	1	1
1	1	0	0	0
1	1	0	1	1
1	1	1	0	1
1	1	1	1	0

## Cell Size

CellName	Height(um)	Width(um)
LVT_XOR4HSV1	1.26	5.32
LVT_XOR4HSV2	1.26	5.32

## Pin Power (uW/MHz)

Pin	V1	V2
A1	0.00338	0.00348
A2	0.00410	0.00420
A3	0.00291	0.00300
A4	0.00359	0.00367

### Pin Capacitance (pf)

Pin	V1	V2
A1	0.00106	0.00106
A2	0.00068	0.00067
A3	0.00105	0.00105
A4	0.00068	0.00067

### Max Leakage Power (uW)

V1	V2
0.01390013	0.01414299

### Delay Table (ns)

Description	V1	V2
A1→Z_FALL	0.08971	0.09063
A1→Z_RISE	0.08773	0.08711
A2→Z_FALL	0.10787	0.10872
A2→Z_RISE	0.10590	0.10521
A3→Z_FALL	0.07523	0.07555
A3→Z_RISE	0.07748	0.07646
A4→Z_FALL	0.09357	0.09375
A4→Z_RISE	0.09591	0.09474